



HY11P13 Datasheet

**8-Bit RISC-like Mixed Signal Microcontroller
Embedded 4x20 LCD Driver
Low Noise Amplifier
18-Bit $\Sigma\Delta$ ADC**

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1. Features

- 8-bit RISC, 66 instructions included.
- Operating voltage range: 2.2V to 3.6V, operation temperature range: -40°C ~85°C.
- External Crystal Oscillator and Internal High Precision RC Oscillator, 6 CPU clock rates enable users to have the most power-saving plan.
 - Active Mode 300uA@2MHz
 - Standby Mode 3uA@32KHz
 - Sleep Mode 1uA
- 4K Word OTP (One Time Programmable) Type program memory, 256 Byte Data Memory.
- Brownout detector and Watch dog Timer, prevents CPU from Crash.
- 18-bit fully differential input Sigma-Delta Analog-to-Digital Converter (A/D)
 - Build-in PGA (Programmable Gain Amplifier) 1/4x、1/2x、1x...128x, 10 input signal gain selection.
 - Build-in Input zero adjustment can increase measurement range according to different application.
 - Built-in high impedance input buffer (Not suitable for 32x or upwards input gain).
 - Built-in absolute temperature sensor
- Ultra-Low Input Noise (<1uVpp) OP provides high output impedance, small signal amplification and low current voltage transformation.
- 1.0 V internal analog circuit common ground that equips with Push-Pull drive ability to provide sensor driving voltage.
- LVD low voltage detection function has 14 steps of voltage detection configuration and external input voltage detection function.
- VDDA can select 4 different output voltage that equips with 10mA low dropout regulator function.
- 4x20 LCD driver
 - Static、1/2、1/3、1/4 Duty and 1/3 Bias programmable option.
 - Built-in Charge Pump regulated circuit, providing 4 LCD Bias voltage.
- 8-bit Timer A
- 16-bit Timer B module has Capture/ Compare function.
- 8-bit Timer C module can generate PWM/PFD waveform.
- Serial communication SPI module
- Support 6 stack level

2. Pin Definition

2.1. 64PIN Diagram LQFP64

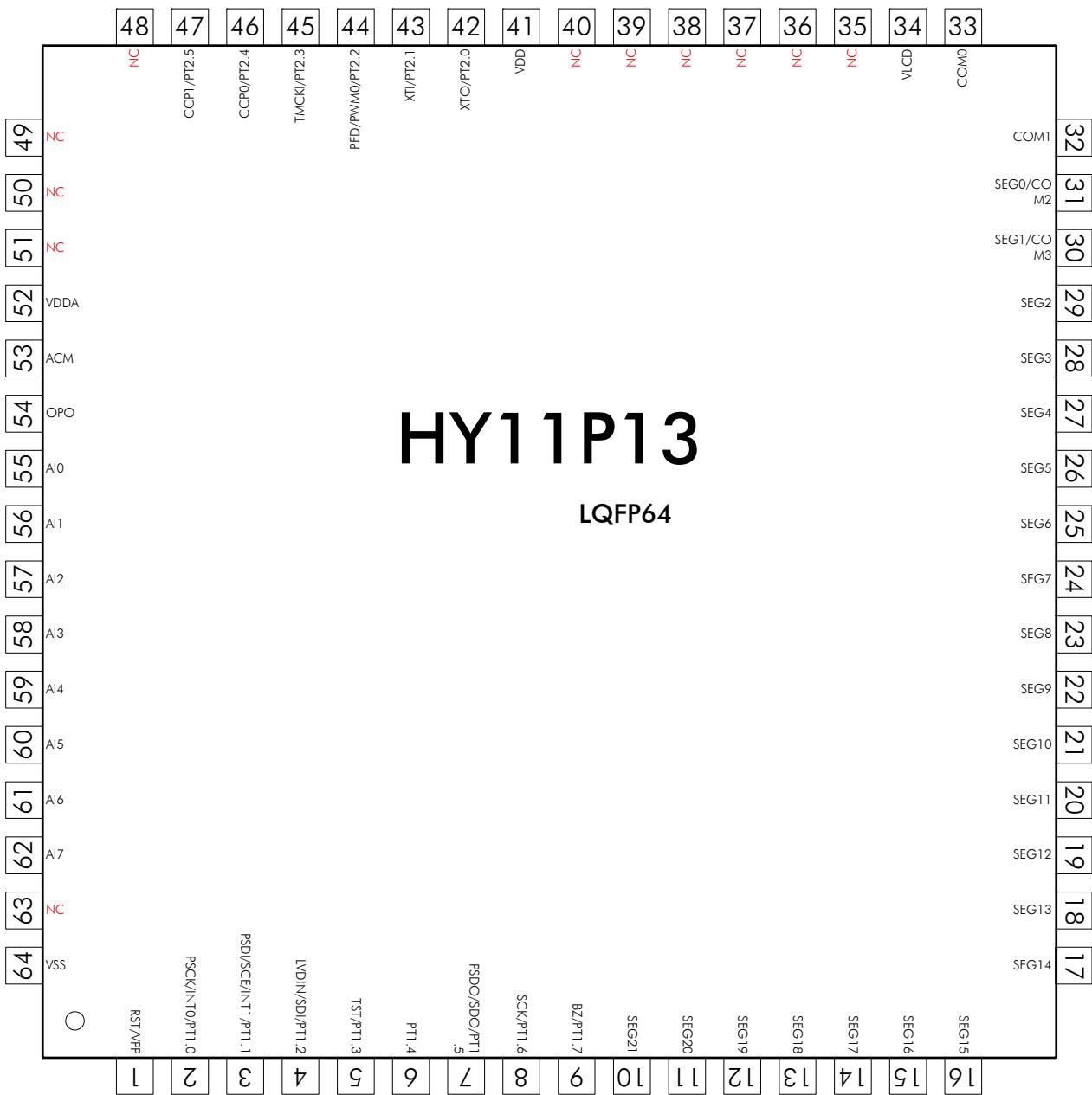


Figure 2-1 HY11P13 LQFP64 Pin Diagram

Note 1 : VPP and RST use the same pin. Input voltage cannot exceed 5.8V when not programming EPROM.

Note 2 : TST and PT1.3 use the same pin. Input voltage cannot exceed Vdd+0.3V while operating.

Note 3 : If PT1.3 is not configured as external button pin, the anti-interference ability will be enhanced.

2.2. LQFP64 Pinout I/O Description

"I/O" input/output, "I" input, "O" output, "S" Smith Trigger, "C" CMOS features compatible input/output, "P" power supply, "A" analog channel

NO.	Pin Name	Pin Characteristic		Description
		Pin Type	Buffer Type	
1	RST/VPP			
	RST	I	S	Reset IC
	VPP	P	P	EPROM programming voltage input
2	PT1.0/INT0/PSCK			
	PT1.0	I	S	Digital input
	INT0	I	S	Interrupt input INT0
	PSCK	I	S	OTP programming interface SCK
3	PT1.1/INT1/PSDI/SCE			
	PT1.1	I	S	Digital input
	INT1	I	S	Interrupt input INT 1
	PSDI	I	S	OTP programming interface SDI
	SCE	I	S	SPI communication interface SCE
4	PT1.2/SDI/LVDIN			
	PT1.2	I	S	Digital input
	SDI	I/O	S	SPI communication interface SDI
	LVDIN	A	A	LVD external signal input interface
5	PT1.3/TST			
	PT1.3	I	S	Digital input
	TST	I	S	Test Mode input pin (invalid)
6	PT1.4	I/O	S	Digital output
7	PT1.5/PSDO/SDO			
	PT1.5	I/O	S	Digital I/O
	PSDO	O	C	OTP programming interface SDO
	SDO	I/O	S	SPI communication interface SDO
8	PT1.6/SCK			
	PT1.6	I/O	S	Digital input/output
	SCK	I/O	S	SPI communication interface SCK
9	PT1.7/BZ			
	PT1.7	I/O	S	Digital I/O
	BZ	O	C	Buzzer output
10	SEG21	O	A	Segment output for LCD
11	SEG20	O	A	Segment output for LCD
12	SEG19	O	A	Segment output for LCD

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13	SEG18	O	A	Segment output for LCD
14	SEG17	O	A	Segment output for LCD
15	SEG16	O	A	Segment output for LCD
16	SEG15	O	A	Segment output for LCD
17	SEG14	O	A	Segment output for LCD
18	SEG13	O	A	Segment output for LCD
19	SEG12	O	A	Segment output for LCD
20	SEG11	O	A	Segment output for LCD
21	SEG10	O	A	Segment output for LCD
22	SEG9	O	A	Segment output for LCD
23	SEG8	O	A	Segment output for LCD
24	SEG7	O	A	Segment output for LCD
25	SEG6	O	A	Segment output for LCD
26	SEG5	O	A	Segment output for LCD
27	SEG4	O	A	Segment output for LCD
28	SEG3	O	A	Segment output for LCD
29	SEG2	O	A	Segment output for LCD
30	COM3/SEG1	O	A	COM/segment output for LDO
31	COM2/SEG0	O	A	COM/segment output for LDO
32	COM1	O	A	COM output for LDO
33	COM0	O	A	COM output for LDO
34	VLCD	P	P	Power supply for LDO
35	NC	-	-	Unused
36	NC	-	-	Unused
37	NC	-	-	Unused
38	NC	-	-	Unused
39	NC	-	-	Unused
40	NC	-	-	Unused
41	VDD	P	P	Power supply for IC operation
42	PT2.0/XTO PT2.0 XTO	I/O A	S A	Digital I/O External oscillator output
43	PT2.1/XTI PT2.1 XTI	I/O A	S A	Digital I/O External oscillator input
44	PT2.2/PWM0/PFD PT2.2 PWM0	I/O O	C C	Digital I/O PWM output

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		PFD	O	C	PFD output
45	PT2.3/TMCKI PT2.3 TMCKI	I/O I	S S	Digital I/O TIMERC clock source input	
46	PT2.4/CCP0 PT2.4 CCP0	I/O I	S S	Digital I/O CCP mode signal interface	
47	PT2.5/CCP1 PT2.5 CCP1	I/O I	S S	Digital I/O CCP mode signal interface	
48	NC	-	-	Unused	
49	NC	-	-	Unused	
50	NC	-	-	Unused	
51	NC	-	-	Unused	
52	VDDA	P	P	Regulator output Analog circuit voltage source	
53	ACM	P	P	Internal analog circuit common ground pin	
54	OPO	A	A	OP output	
55	AI0	A	A	Analog channel pin	
56	AI1	A	A	Analog channel pin	
57	AI2	A	A	Analog channel pin	
58	AI3	A	A	Analog channel pin	
59	AI4	A	A	Analog channel pin	
60	AI5	A	A	Analog channel pin	
61	AI6	A	A	Analog channel pin	
62	AI7	A	A	Analog channel pin	
63	NC	-	-	Unused	
64	VSS	P	P	Grounding pin for IC operation voltage	

Table 2-1 Pin Definition and Function Description

3. Application Circuit

3.1. Bridge Sensor I

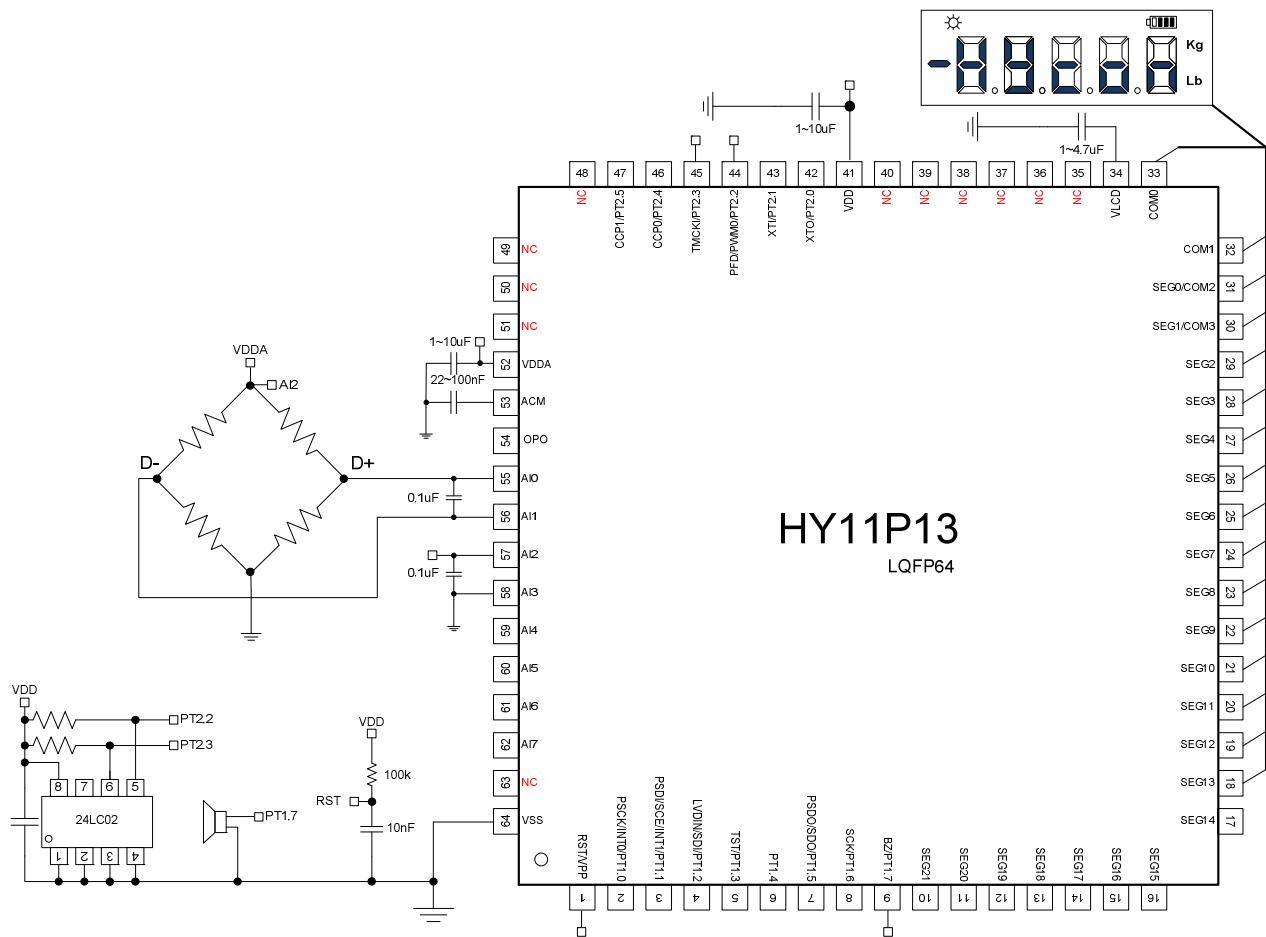


Figure 3-1 Bridge Sensor Application Circuit

Note 1 : DCSET[2:0] can conduct bias adjustment of Load Cell zero point voltage address

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3.2. Bridge Sensor II

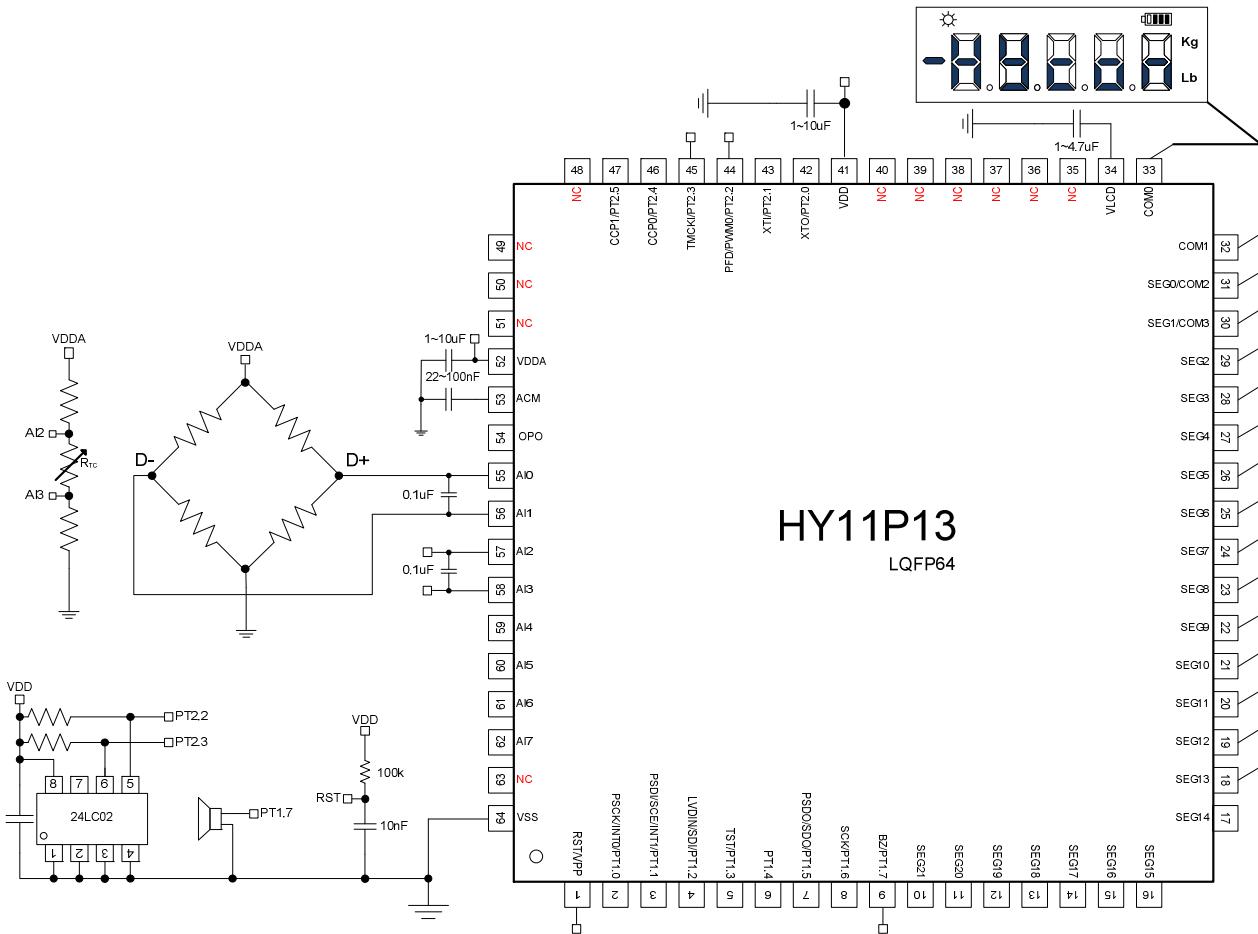


Figure 3-2 Application Circuit of Temperature Compensation Bridge Sensor

Note 1 : Using temperature compensation resistor NTC basic circuit

Note 2 : DCSET[2:0] can conduct bias adjustment of Load Cell zero point voltage address

3.3. Bridge Sensor (Pressure Sensor)

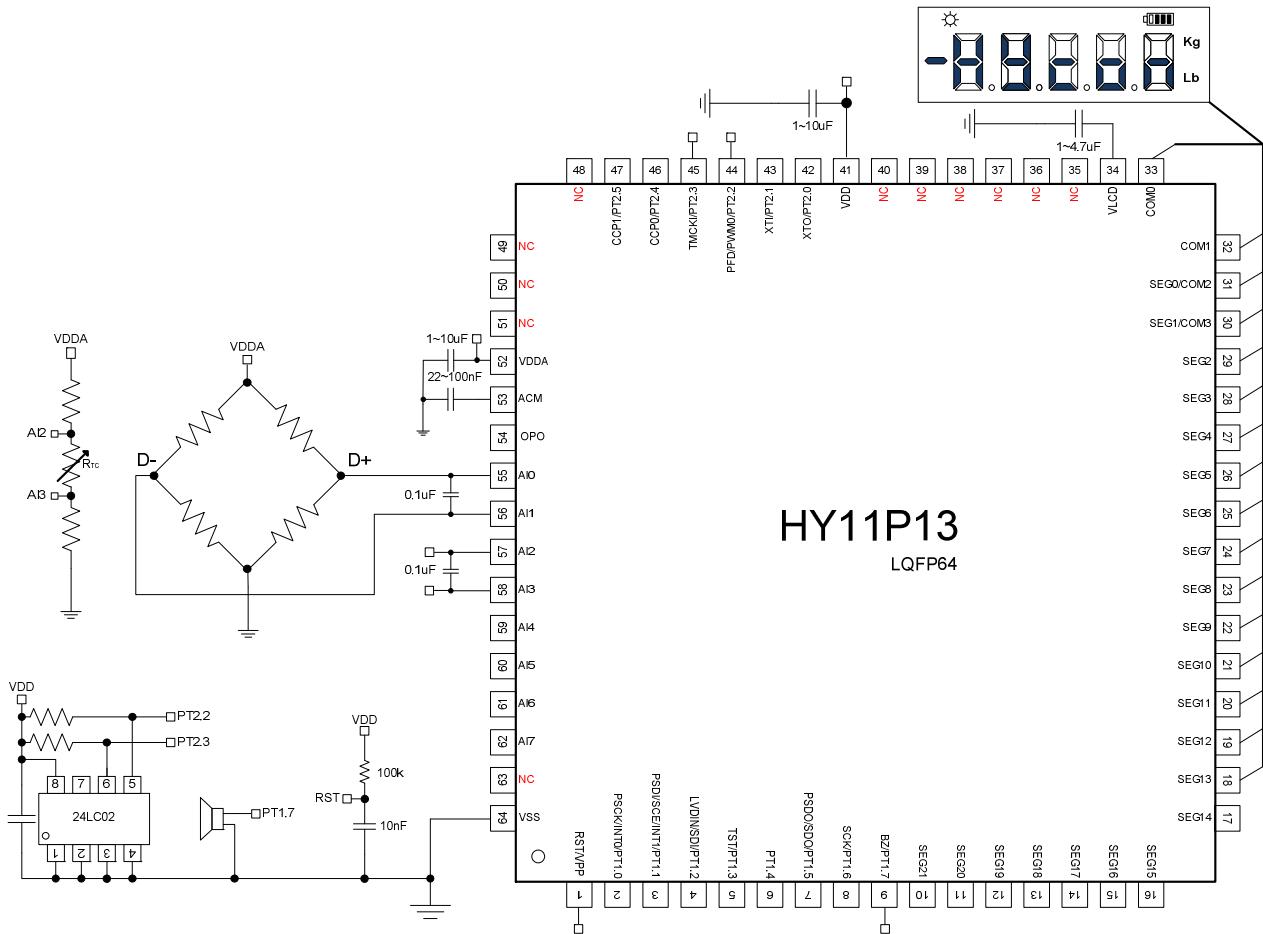


Figure 3-3 Temperature Compensative Bridge Sensor Application Circuit (wo/ internal PGA amplification)

Note 1 : Using temperature compensation resistor NTC basic circuit

Note 2 : Pressure sensor zero point voltage address can be configured through DCSET[2:0] bias adjustment.

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3.4. IR Sensor

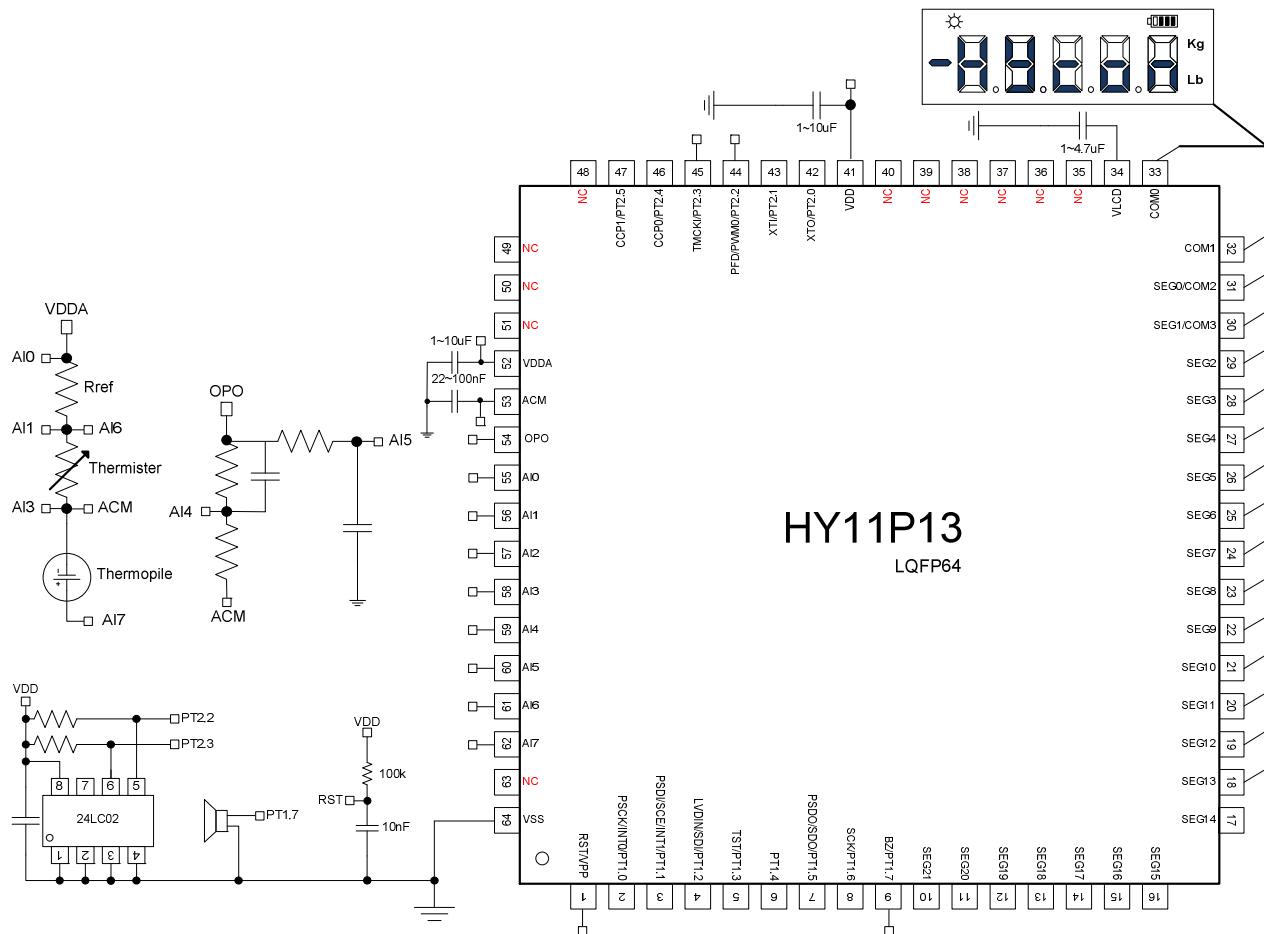
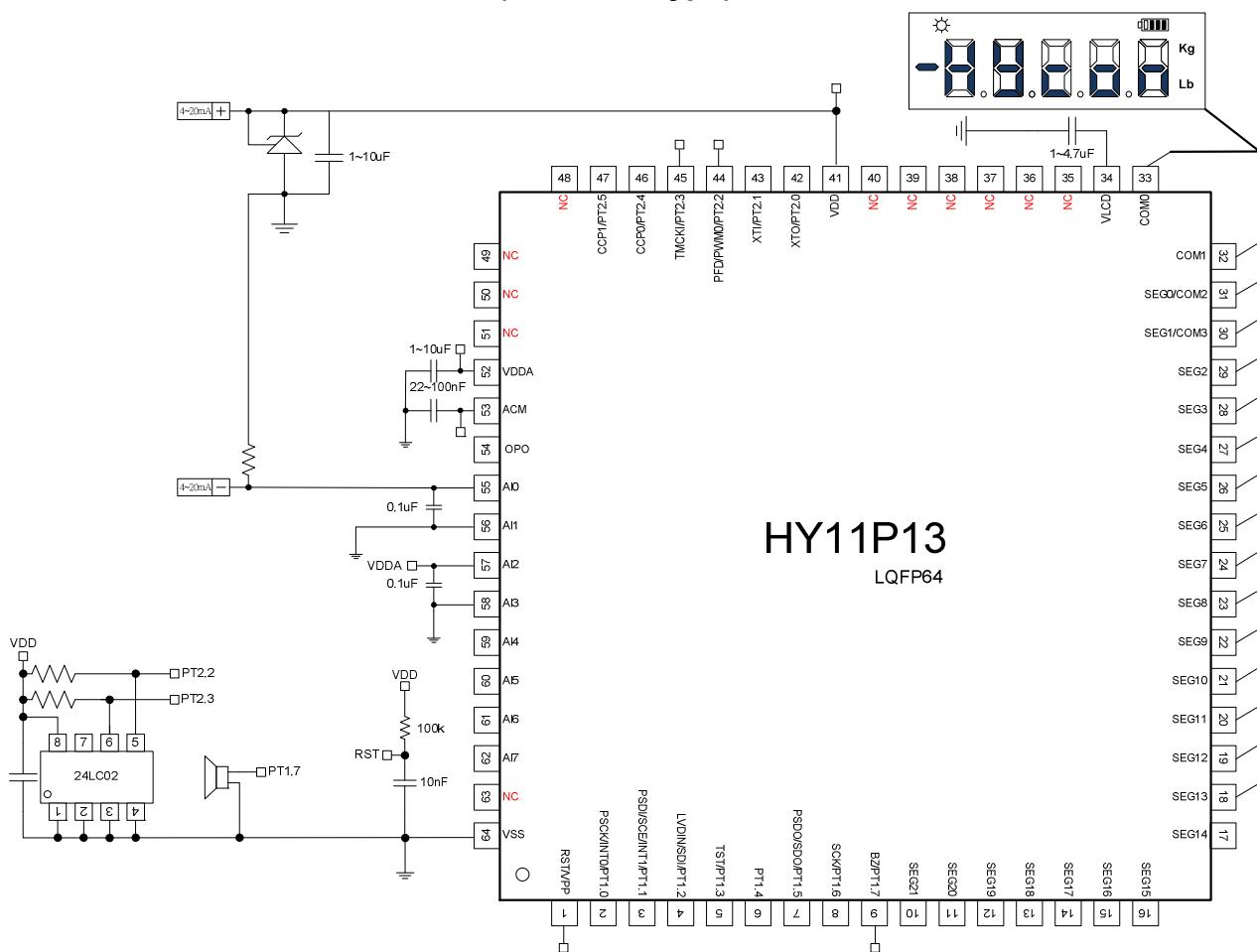


Figure 3-4 IR Sensor Application Circuit

3.5. 4-20mA Current Panel Meter (Two-wire Type)



4. Function Outline

4.1. Internal Block Diagram

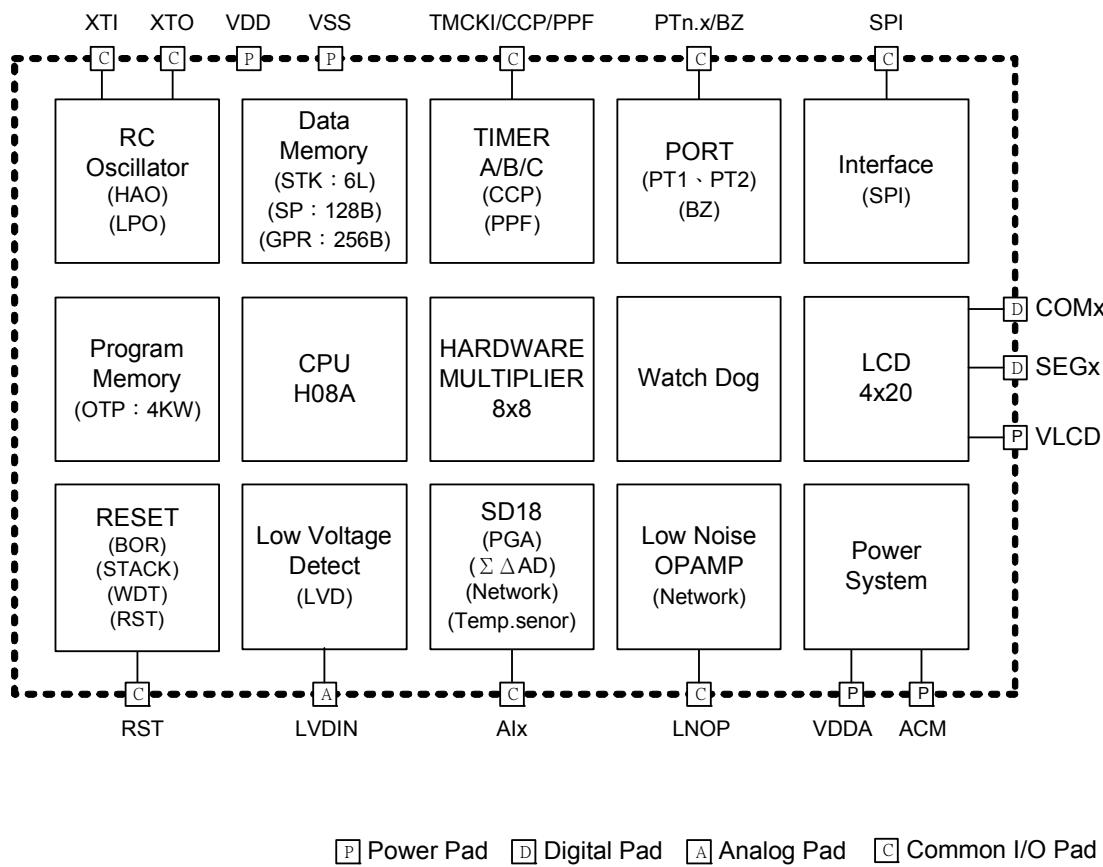


Figure 4-1 HY11P13 Internal Block Diagram

4.2. Related Description and Supporting Documents

IC Function Related Operating Instruction

DS-HY11P13-Vxx HY11P13 Data Sheet

UG-HY11S14-Vxx HY11P Series Users' Manual

APD-CORE002-Vxx H08A Instruction Description

Development Tool Related Operating Instruction

APD-HYIDE006-Vxx HY11xxx Series Development Tool Software Instruction Manual

APD-HYIDE005-Vxx HY11xxx Series Development Tool Hardware Instruction Manual

APD-OTP001-Vxx OTP Products Programming Pin Manual

Product Production Related Operating Instruction

APD-HYIDE004-Vxx HY1xxxx Series Production Line Specialized Programmer Manual

BDI-HY11P13-Vxx HY11P13 Individual Product Die Bonding Information

4.3. SD18 Network

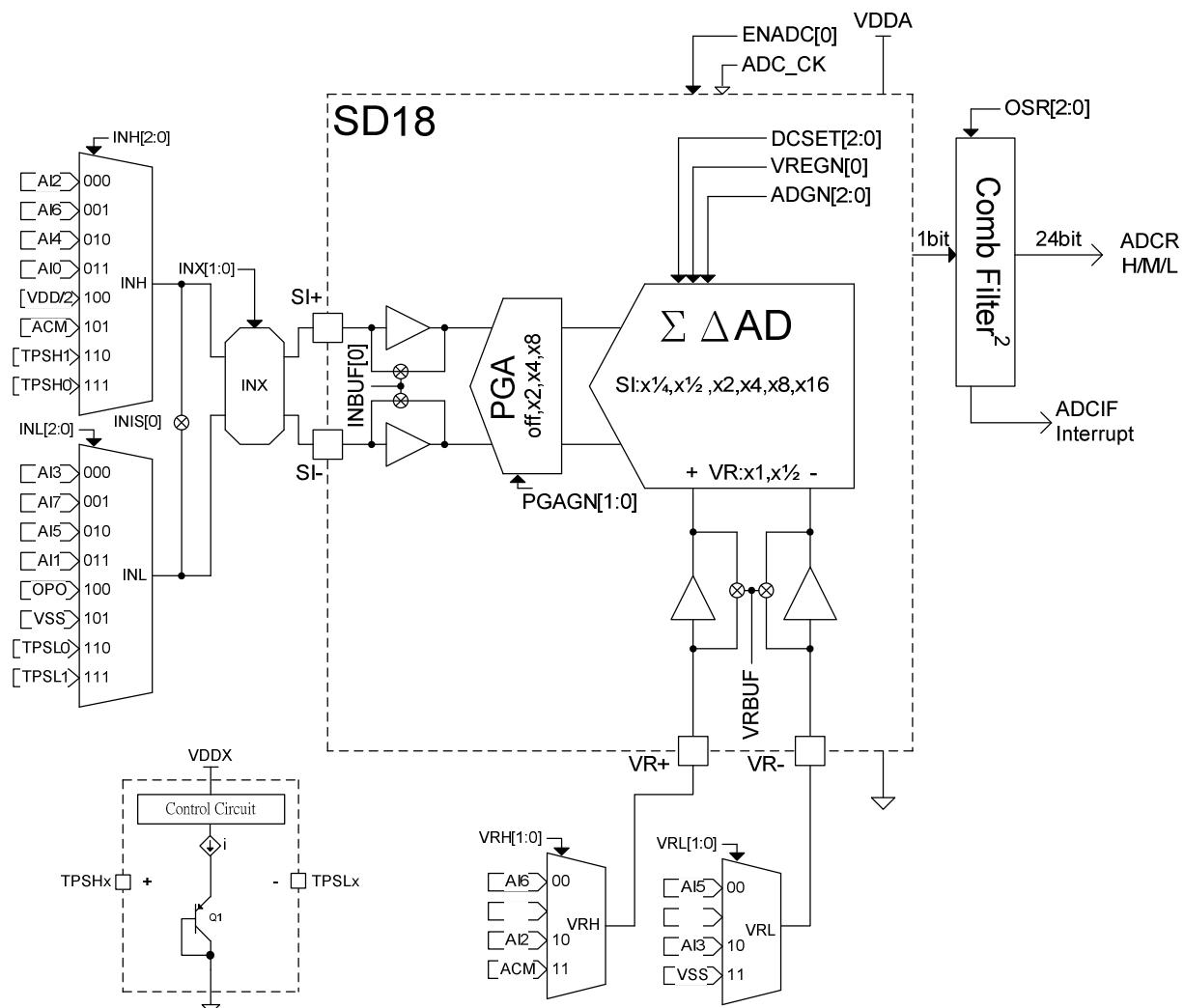


Figure 4-2 SD18 Network

4.4. Low Noise OPAMP Network

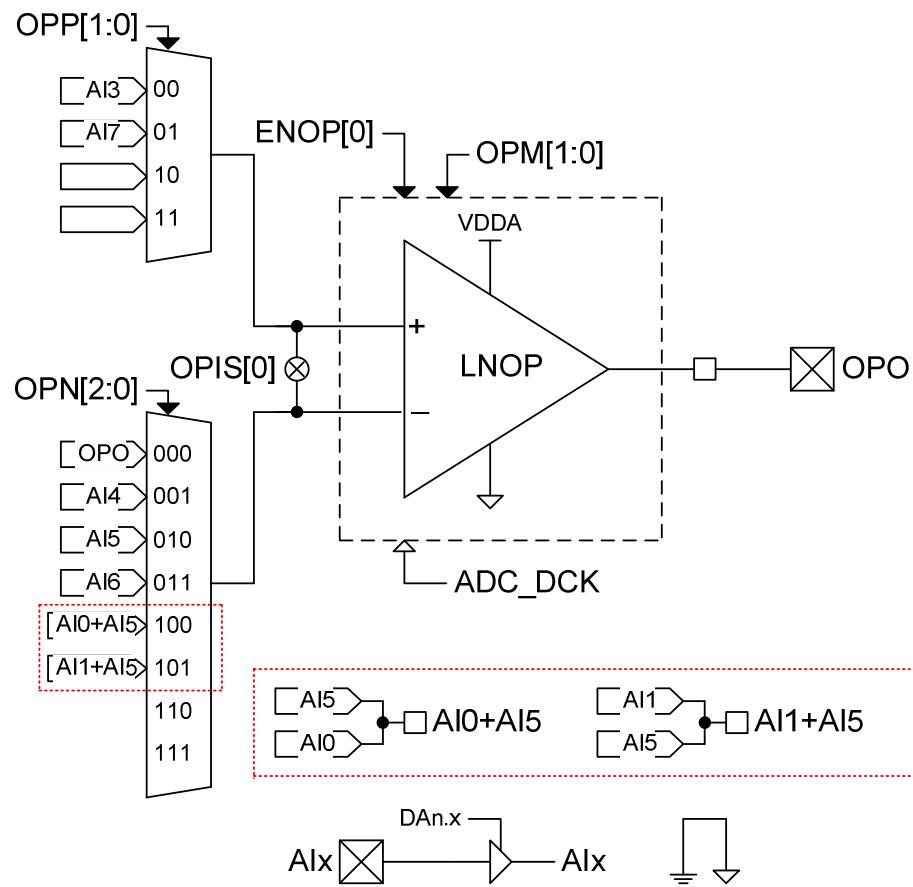


Figure 4-3 Low Noise OPAMP Network

5. Register List

"-no use,""read/write,"w"write,"r"read,"r0"only read 0,"r1"only read 1,"w0"only write 0,"w1"only write 1 .unimplemented bit,"x"unknown,"u"unchanged,"d"depends on condition																				
Address	File Name	Bit7	Bit6	Bit5	Bit4	Bit3	Bit2	Bit1	Bit0	A-RESET	I-RESET	R/W								
00H	INDF0	Contents of FSR0 to address data memory value of FSR0 not changed								N/A	N/A	*****,*								
01H	POINC0	Contents of FSR0 to address data memory value of FSR0 post-incremented								N/A	N/A	*****,*								
02H	PODEC0	Contents of FSR0 to address data memory value of FSR0 post-decremented								N/A	N/A	*****,*								
03H	PRINCO	Contents of FSR0 to address data memory value of FSR0 pre-incremented								N/A	N/A	*****,*								
04H	PLUSW0	Contents of FSR0 to address data memory value of FSR0 offset by W								N/A	N/A	*****,*								
05H	INDF1	Contents of FSR1 to address data memory value of FSR0 not changed								N/A	N/A	*****,*								
06H	POINC1	Contents of FSR1 to address data memory value of FSR0 post-incremented								N/A	N/A	*****,*								
07H	PODEC1	Contents of FSR1 to address data memory value of FSR0 post-decremented								N/A	N/A	*****,*								
08H	PRINC1	Contents of FSR1 to address data memory value of FSR0 pre-incremented								N/A	N/A	*****,*								
09H	PLUSW1	Contents of FSR1 to address data memory value of FSR0 offset by W								N/A	N/A	*****,*								
0FH	FSR0H								xu	-,-,-,-,-,-*								
10H	FSR0L	Indirect Data Memory Address Pointer 0 Low Byte,FSR0[7:0]								xxxx xxxx	uuuu uuuu	*****,*								
11H	FSR1H								xu	-,-,-,-,-,-*								
12H	FSR1L	Indirect Data Memory Address Pointer 1 Low Byte,FSR1[7:0]								xxxx xxxx	uuuu uuuu	*****,*								
16H	TOSH								00000000	-,-,-,-,-,-*								
17H	TOSL	Top-of-Stack Low Byte (TOS<7:0>)								0000 0000	0000 0000	*****,*								
18H	STKPTR	STKF1	STKUN	STKOV																
1AH	PCLATH									PC[11]	PC[10]	PC[9]	PC[8]							
1BH	PCLATL	PC Low Byte for PC<7:0>								0000 0000	0000 0000	*****,*								
1DH	TBLPTRH									TBLPTR[11]	TBLPTR[10]	TBLPTR[9]	TBLPTR[8]							
1EH	TBLPTRL	Program Memory Table Pointer Low Byte (TBLPTR<7:0>)								0000 0000	0000 0000	*****,*								
1FH	TBLDLH	Program Memory Table Latch High Byte								0000 0000	0000 0000	*****,*								
20H	TBLDL	Program Memory Table Latch Low Byte								0000 0000	0000 0000	*****,*								
21H	PRODH	Product Register of Multiply High Byte								xxxx xxxx	uuuu uuuu	r,r,r,r,r,r,r,r								
22H	PRODL	Product Register of Multiply Low Byte								xxxx xxxx	uuuu uuuu	r,r,r,r,r,r,r,r								
23H	INTE1	GIE	ADCIE	TMCIE	TMBIE	TMAIE	WDTIE	E1IE	E0IE	0000 0000	0000 0000	*****,*								
24H	INTE2	TXIE	RCIE								000000							
26H	INTF1									SSPIE	CCP1IE	CCPOIE								
27H	INTF2									WDTIF	E1IF	E0IF								
29H	WREG	Working Register								SSPIF	CCP1IF	CCPOIF								
2AH	BSRCN									BSR[0]00								
2BH	STATUS									C	DC	N	OV	Z						
2CH	PSTATUS	PD	TO	IDLEB	BOR															
2DH	LVDCN									LVDFG	LVD	LVDON	VLDX[3:0]							
30H	PWRCN	ENVDDA	VDDAX[1:0]								ENACM									
31H	MCKCN1									ADCC1	XTHSP	XTSP	ENXT	ENHAO						
32H	MCKCN2									HSCK	HSS[1:0]	CPUCK[1:0]								
33H	MCKCN3									LSCK	PERCK	BZS[2:0]								
37H	OPCN1	ENOP	OPM[1:0]									OPN[2:0]	OPN[2:0]							
39H	ADCRH	ADC conversion memory HighByte								xxxx xxxx	uuuu uuuu	r,r,r,r,r,r,r,r								
3AH	ADCRM	ADC conversion memory Middle Byte								xxxx xxxx	uuuu uuuu	r,r,r,r,r,r,r,r								
3BH	ADCRL	ADC conversion memory Low Byte								xxxx xxxx	uuuu uuuu	r,r,r,r,r,r,r,r								
3CH	ADCCN1	ENADC	ENHIGN	ENCHP	PGAGN[1:0]								ADGN[2:0]							
3DH	ADCCN2									INBUF	VRBUF	VREGN	DCSET[2:0]							
3EH	ADCCN3									OSR[2:0]										
3FH	AINET1									INH[2:0]	INL[2:0]									
40H	AINET2									VRH[1:0]	INX[1:0]									
41H	TMACN	ENTMA	TMACK	TMAS[1:0]								ENWDT	WDTS[2:0]							
42H	TMAR	TimerA data register								TMBSY	TMBR2R									
43H	TMBCN	ENTMB	TMBCK	TMBS[1:0]								TMBSY	TMBR2R							
44H	TMBRH	TimerB High Byte data register								TMBSY	TMBR2R									
45H	TMBRL	TimerB Low Byte data register								TMBSY	TMBR2R									
46H	TMCCN	ENTMC	TMCKC1[1:0]	TMCS1[2:0]								TMCS0[1:0]	TMCS0[1:0]							
47H	PRC	TimerC programmable register								TMCS1[2:0]	TMCS0[1:0]									
48H	TMCR	TimerC register								TMCS0[1:0]	TMCS0[1:0]									
49H	CCPCN									CCP1M[3:0]	CCP0M[3:0]									
4AH	CCP0RH	CCP0 High Byte data register								CCP0M[3:0]	CCP0M[3:0]									
4BH	CCP0RL	CCP0 Low Byte data register								CCP0M[3:0]	CCP0M[3:0]									
4CH	CCP1RH	CCP1 High Byte data register								CCP1M[3:0]	CCP1M[3:0]									
4DH	CCP1RL	CCP1 Low Byte data register								CCP1M[3:0]	CCP1M[3:0]									
4EH	PASC	PASF	PASCF[1:0]								0.00	0.00								
4FH	PWMCN	ENPWM	ENPFD	PWMRL[1:0]								0.00	0.00							
51H	PWMR	PWM MSB Byte register								xxxx xxxx	uuuu uuuu								*****,*	

Table 5-1(a) HY11P13 Register List

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"-"no use,"**"read/write,"w"write,"r"read,"r0"only read 0,"r1"only read 1,"w0"only write 0,"w1"only write 1 .unimplemented bit,"x"unknown,"u"unchanged,"d"depends on condition											A-RESET	I-RESET	R/W
Address	File Name	Bit7	Bit6	Bit5	Bit4	Bit3	Bit2	Bit1	Bit0	A-RESET	I-RESET	R/W	
52H	LDCCN1	ENLCD	LCDPR	VLCDX[1:0]		LCDBF	LCDBI[1:0]			0000 000.	0000 000.	*****,-,-	
53H	LDCCN2	LCDBL	LCDMX[1:0]							000....	000....	****,-,-,-	
54H	LCD0	Segment SEG2@[3:0] and SEG3@[7:4] data register of LCD								xxxx xxxx	uuuu uuuu	*****,-,-	
55H	LCD1	Segment SEG4@[3:0] and SEG5@[7:4] data register of LCD								xxxx xxxx	uuuu uuuu	*****,-,-	
56H	LCD2	Segment SEG6@[3:0] and SEG7@[7:4] data register of LCD								xxxx xxxx	uuuu uuuu	*****,-,-	
57H	LCD3	Segment SEG8@[3:0] and SEG9@[7:4] data register of LCD								xxxx xxxx	uuuu uuuu	*****,-,-	
58H	LCD4	Segment SEG10@[3:0] and SEG11@[7:4] data register of LCD								xxxx xxxx	uuuu uuuu	*****,-,-	
59H	LCD5	Segment SEG12@[3:0] and SEG13@[7:4] data register of LCD								xxxx xxxx	uuuu uuuu	*****,-,-	
5AH	LCD6	Segment SEG14@[3:0] and SEG15@[7:4] data register of LCD								xxxx xxxx	uuuu uuuu	*****,-,-	
5BH	LCD7	Segment SEG16@[3:0] and SEG17@[7:4] data register of LCD								xxxx xxxx	uuuu uuuu	*****,-,-	
5CH	LCD8	Segment SEG18@[3:0] and SEG19@[7:4] data register of LCD								xxxx xxxx	uuuu uuuu	*****,-,-	
5DH	LCD9	Segment SEG20@[3:0] and SEG21@[7:4] data register of LCD								xxxx xxxx	uuuu uuuu	*****,-,-	
5EH	SSPCON1	SSPEN	CKP	CKE	SMP				SSPM<1:0>	0000 ..00	uuuu ..uu	*****,-,-	
60H	SSPSTA	SSPBUT	SSPOV						BF	00...0	00...00	r,r,-,-,-,-r	
61H	SSPBUF	SSP Receive Buffer/Transmit Register										*****,-,-	
6DH	PT1	PT1.7	PT1.6	PT1.5	PT1.4	PT1.3	PT1.2	PT1.1	PT1.0	xxxx xxxx	uuuu uuuu	****,-r,r,r	
6EH	TRISC1	TC1.7	TC1.6	TC1.5	TC1.4					0000	0000	****,-,-,-	
6FH	PT1DA						DA1.2		0..0..	-,-,-,-,-,-*	
70H	PT1PU	PU1.7	PU1.6	PU1.5	PU1.4	PU1.3	PU1.2	PU1.1	PU1.0	0000 0000	0000 0000	*****,-,-	
71H	PT1M1					INTEG1[1:0]		INTEG0[1:0]	00000000	-,-,-,-,-,-*	
72H	PT1M2		PM1.7[0]		PM1.6[0]		PM1.5[0]			.0.0..	.0.0..0..	-,-,-,-,-,-	
74H	PT2			PT2.5	PT2.4	PT2.3	PT2.2	PT2.1	PT2.0	.xx xxxx	..uu uuuu	-,-,-,-,-,-	
75H	TRISC2			TC2.5	TC2.4	TC2.3	TC2.2	TC2.1	TC2.0	..00 0000	..00 0000	-,-,-,-,-,-*	
77H	PT2PU			PU2.5	PU2.4	PU2.3	PU2.2	PU2.1	PU2.0	..00 0000	..00 0000	-,-,-,-,-,-	
78H	PT2M1			PM2.2[1]	PM2.2[0]					..0000	-,-,-,-,-,-	
79H	PT2M2	PWMTR[1]	PWMTR[0]			PM2.5[1]	PM2.5[0]	PM2.4[1]	PM2.4[0]	00..0000	00..0000	*,-,-,-,-,-	
80H ~ FFH	GPR0	General Purpose Register as 128Byte								xxxx xxxx	uuuu uuuu	*****,-,-	
100H~17FH	GPR1	General Purpose Register as 128Byte								xxxx xxxx	uuuu uuuu	*****,-,-	

Figure 5-1(b) HY11P13 Register List (continued)

6. Electrical Characteristics

Absolute maximum ratings over operating free-air temperature (unless otherwise noted)

Voltage applied at V_{DD} to V_{SS}	-0.2 V to 4.0 V
Voltage applied to any pin	-0.2 V to V_{DD} + 0.3 V
Voltage applied to RST/VPP pin	-0.2 V to 6.9 V
Voltage applied to TST/PT1.3 pin	-0.2 V to V_{DD} + 1 V
Diode current at any device terminal	± 2 mA
Storage temperature, Tstg: (unprogrammed device)	-55°C to 150°C
(programmed device)	-40°C to 85°C
Total power dissipation	0.5w
Maximum output current sink by any PORT1 to PORT3 I/O Pin.....	.25mA

6.1. Recommended operating conditions

$T_A = -40^\circ\text{C} \sim 85^\circ\text{C}$, unless otherwise noted

Sym.	Parameter		Test Conditions		Min.	Typ.	Max.	unit	
V_{DD}	Supply Voltage		All digital peripherals and CPU		2.2	3.6		V	
			Analog peripherals		2.4	3.6			
V_{SS}	Supply Voltage				0	0			
XT	External	Watch crystal	$V_{DD} = 2.2V$, $ENXT[0]=1$	XTSP[0]=0, XTHSP[0]=0	32.768K			Hz	
	Oscillator	Ceramic resonator		XTSP[0]=1, XTHSP[0]=0	450K				
	Frequency	Crystal		XTSP[0]=1, XTHSP[0]=0	1M				

6.2. Internal RC Oscillator

$T_A = 25^\circ\text{C}$, $V_{DD} = 3.0\text{V}$, unless otherwise noted

Sym.	Parameter	Test Conditions	Min.	Typ.	Max.	unit
HAO	High Speed Oscillator frequency	$\text{ENHAO}[0]=1$	1.8	2.0	2.2	MHz
LPO	Low Power Oscillator frequency	V_{DD} supply voltage be enable LPO	22	28	35	KHz

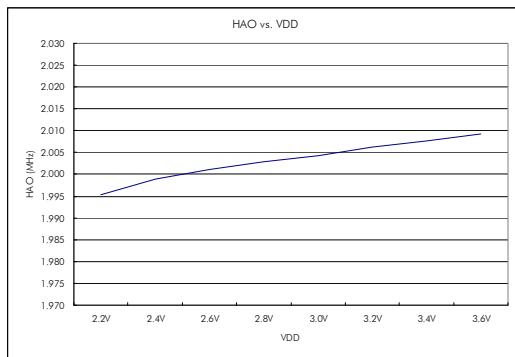


Figure 6.2-1 HAO vs. VDD

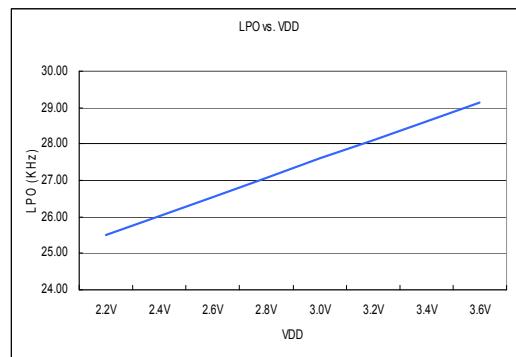


Figure 6.2-2 LPO vs. VDD

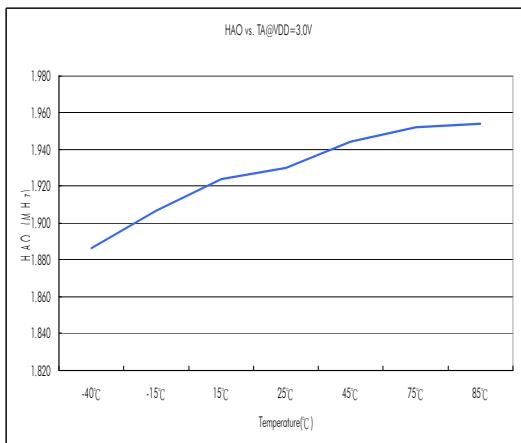


Figure 6.2-3 HAO vs. Temperature

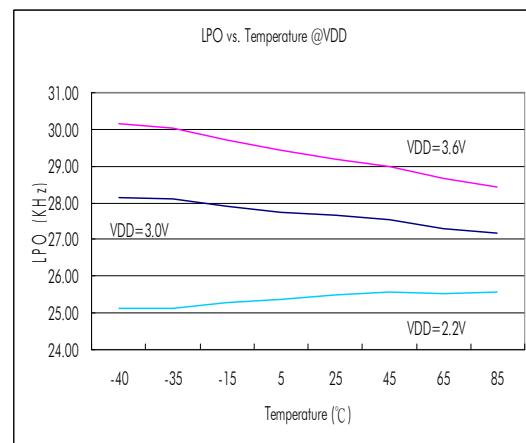


Figure 6.2-4 LPO vs. Temperature

6.3. Supply Current into VDD Excluding Peripherals Current

$T_A = 25^\circ\text{C}$, $V_{DD} = 3.0\text{V}$, $\text{OSC_LPO} = 28\text{KHz}$, unless otherwise noted

Sym.	Parameter	Test Conditions	Min.	Typ.	Max.	unit
I_{AM1}	Active mode 1	$\text{OSC_CY} = 8\text{MHz}$, $\text{OSC_HAO} = \text{off}$, $\text{CPU_CK} = 8\text{MHz}$		1.2	2	mA
I_{AM2}	Active mode 2	$\text{OSC_CY} = \text{off}$, $\text{OSC_HAO} = 2\text{MHz}$, $\text{CPU_CK} = 2\text{MHz}$		0.32	0.55	mA
I_{AM3}	Active mode 3	$\text{OSC_CY} = \text{off}$, $\text{OSC_HAO} = 2\text{MHz}$, $\text{CPU_CK} = 1\text{MHz}$		0.18	0.3	mA
I_{LP1}	Low Power 1	$\text{OSC_CY} = 32768\text{Hz}$, $\text{OSC_HAO} = \text{off}$, $\text{CPU_CK} = 16384\text{Hz}$		7	12	uA
I_{LP2}	Low Power 2	$\text{OSC_CY} = \text{off}$, $\text{OSC_HAO} = \text{off}$, $\text{CPU_CK} = \text{LPO}$, Idle state		1.65	3	uA
I_{LP3}	Low Power 3	$\text{OSC_CY} = \text{off}$, $\text{OSC_HAO} = \text{off}$, $\text{CPU_CK} = \text{off}$, Sleep state		0.65	1.2	uA

OSC_CY : External Oscillator frequency.

OSC_HAO : Internal High Accuracy Oscillator frequency.

CPU_CK : CPU core work frequency.

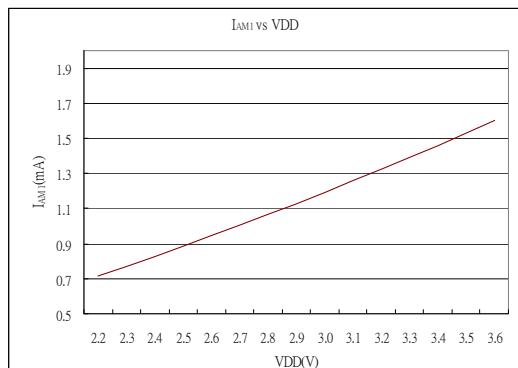


Figure 6.3-1 I_{AM1} vs. VDD

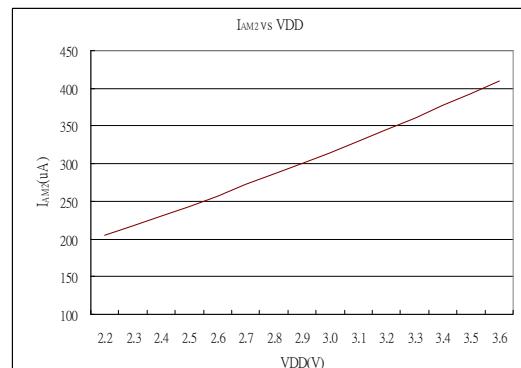


Figure 6.3-2 I_{AM2} vs. VDD

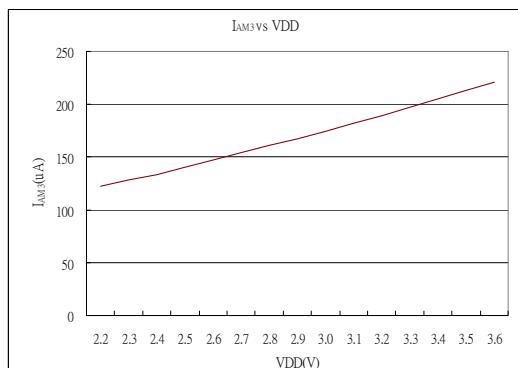


Figure 6.3-3 I_{AM3} vs. VDD

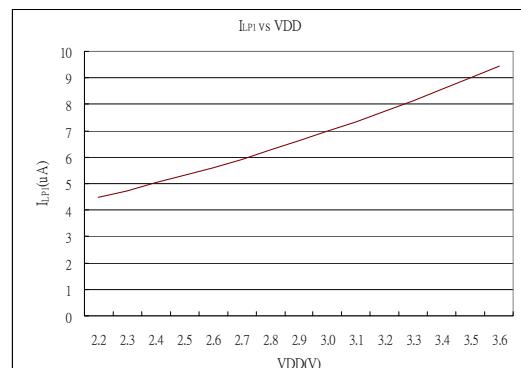


Figure 6.3-4 I_{LP1} vs. VDD

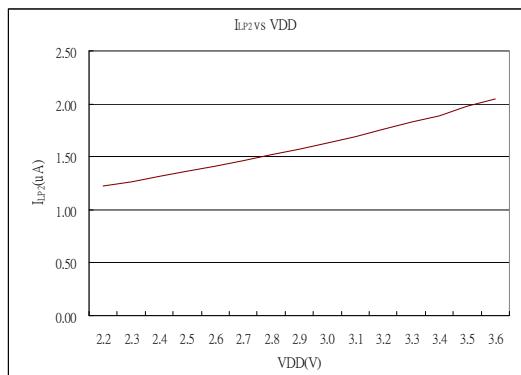


Figure 6.3-5 I_{LP2} vs. VDD

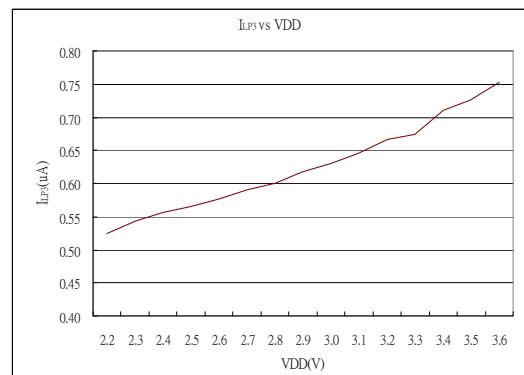


Figure 6.3-6 I_{LP3} vs. VDD

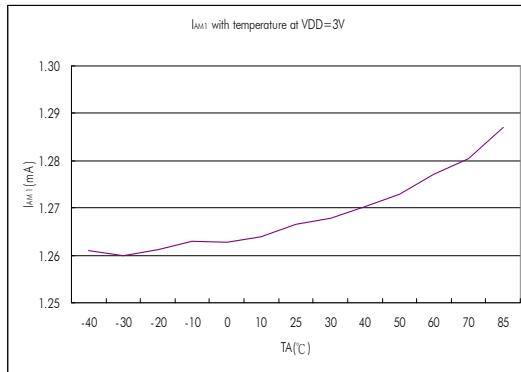


Figure 6.3-7 I_{AM1} vs. Temperature

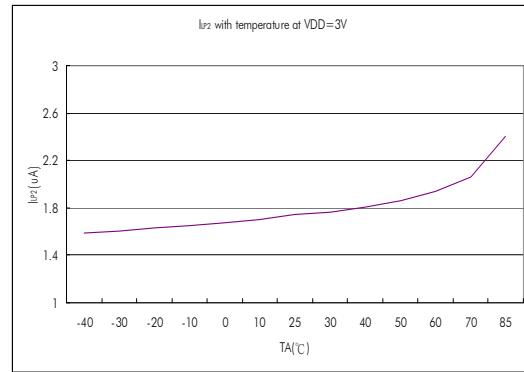


Figure 6.3-8 I_{LP2} vs. Temperature

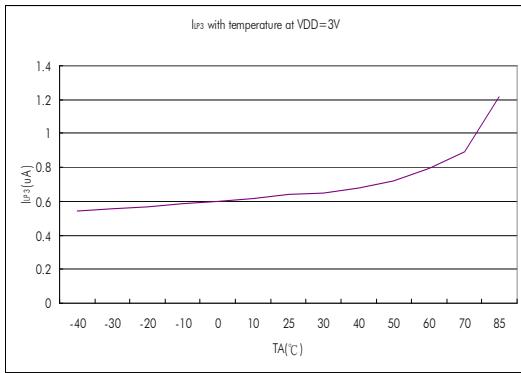


Figure 6.3-9 I_{LP3} vs. Temperature

6.4. Port1~2

$T_A = 25^\circ\text{C}$, $V_{DD} = 3.0\text{V}$, unless otherwise noted

Sym.	Parameter	Test Conditions	Min.	Typ.	Max.	unit
Input voltage and Schmitt trigger and leakage current and timing						
V_{IH}	High-Level input voltage		2.1			V
V_{IL}	Low-Level input voltage		0.9			
V_{hys}	Input Voltage hysteresis($V_{IH} - V_{IL}$)		0.8			V
I_{LKG}	Leakage Current			0.1		uA
R_{PU}	Port pull high resistance		180			kΩ
Output voltage and current and frequency						
V_{OH}	High-level output voltage	$I_{OH}=10\text{mA}$	$V_{DD} - 0.3$			V
V_{OL}	Low-level output voltage	$I_{OL}=-10\text{mA}$				

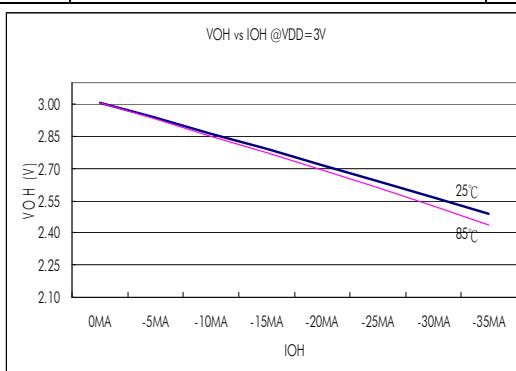


Figure 6.4-1 V_{OH} vs. I_{OH} @ $V_{DD}=3.0\text{V}$

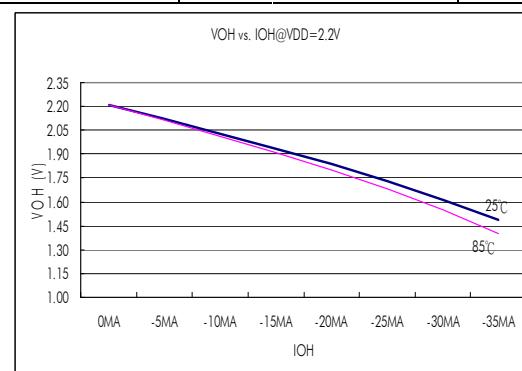


Figure 6.4-2 V_{OH} vs. I_{OH} @ $V_{DD}=2.2\text{V}$

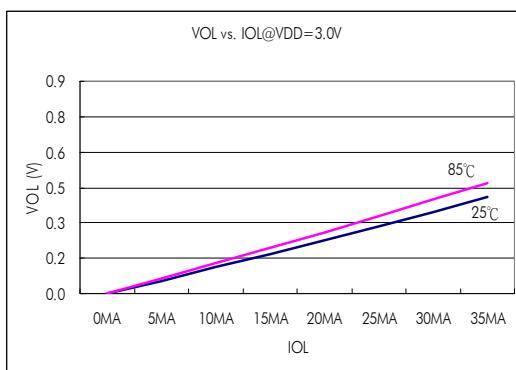


Figure 6.4-3 V_{OL} vs. I_{OL} @ $V_{DD}=3.0\text{V}$

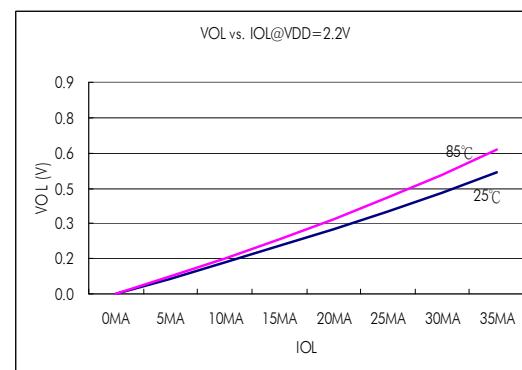


Figure 6.4-4 V_{OL} vs. I_{OL} @ $V_{DD}=2.2\text{V}$

6.5. Reset (Brownout, External RST pin, Low Voltage Detect)

$T_A = 25^\circ\text{C}$, $V_{DD} = 3.0\text{V}$, unless otherwise noted

Sym.	Parameter	Test Conditions	Min.	Typ.	Max.	unit
BOR	Pulse length needed to accepted reset internally, t_{d-LVR}		2			us
	V_{DD} Start Voltage to accepted reset internally ($L \rightarrow H$), V_{LVR}		1.6	1.85	2.1	V
	Hysteresis, $V_{HYS-LVR}$			70		mV
RST	Pulse length needed as RST/VPP pin to accepted reset internally, t_{d-RST}		2			us
	Input Voltage to accepted reset internally		0.9			V
	Hysteresis, $V_{HYS-RST}$			0.8		V
LVD	Operation current, I_{LVD}		10	15		uA
	External input voltage to compare reference voltage		1.2			V
	Compare reference voltage temperature drift	$T_A = -40^\circ\text{C} \sim 85^\circ\text{C}$	100			ppm/°C
	Detect V_{DD} voltage rang by user option, $V_{SVS} VLDx[3:0]=1110b$		3.3			
	Detect V_{DD} voltage rang by user option, $V_{SVS} VLDx[3:0]=1101b$		3.2			
	Detect V_{DD} voltage rang by user option, $V_{SVS} VLDx[3:0]=1100b$		3.1			
	Detect V_{DD} voltage rang by user option, $V_{SVS} VLDx[3:0]=1011b$		3.0			
	Detect V_{DD} voltage rang by user option, $V_{SVS} VLDx[3:0]=1010b$		2.9			
	Detect V_{DD} voltage rang by user option, $V_{SVS} VLDx[3:0]=1001b$		2.8			
	Detect V_{DD} voltage rang by user option, $V_{SVS} VLDx[3:0]=1000b$		2.7			
	Detect V_{DD} voltage rang by user option, $V_{SVS} VLDx[3:0]=0111b$		2.6			
	Detect V_{DD} voltage rang by user option, $V_{SVS} VLDx[3:0]=0110b$		2.5			
	Detect V_{DD} voltage rang by user option, $V_{SVS} VLDx[3:0]=0101b$		2.4			
	Detect V_{DD} voltage rang by user option, $V_{SVS} VLDx[3:0]=0100b$		2.3			
	Detect V_{DD} voltage rang by user option, $V_{SVS} VLDx[3:0]=0011b$		2.2			
	Detect V_{DD} voltage rang by user option, $V_{SVS} VLDx[3:0]=0010b$		2.1			
	Detect V_{DD} voltage rang by user option, $V_{SVS} VLDx[3:0]=0001b$		2.0			
BOR : Brownout Reset						
LVR : Low Voltage Reset of BOR						
LVD : Low Voltage Detect						
RST : External Reset pin						

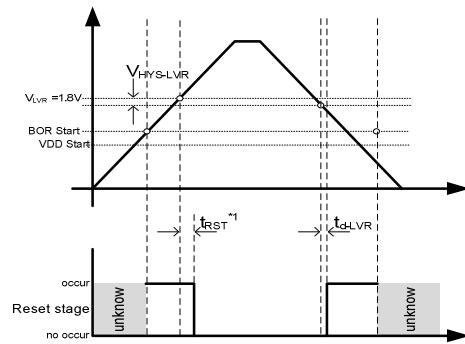


Figure 6.5-1 BOR Reset Diagram

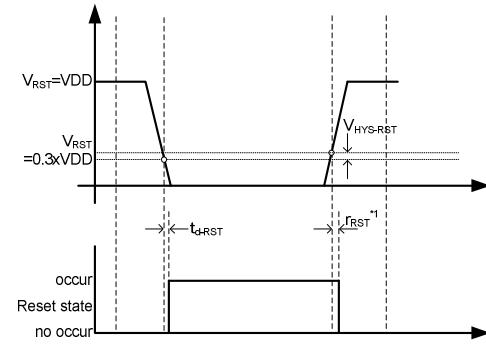


Figure 6.5-2 RST Reset Diagram

1 t_{RST}^ : Please see BOR Introduce of HY11Pxx series User's Guide (UG-HY11S14-Vxx).

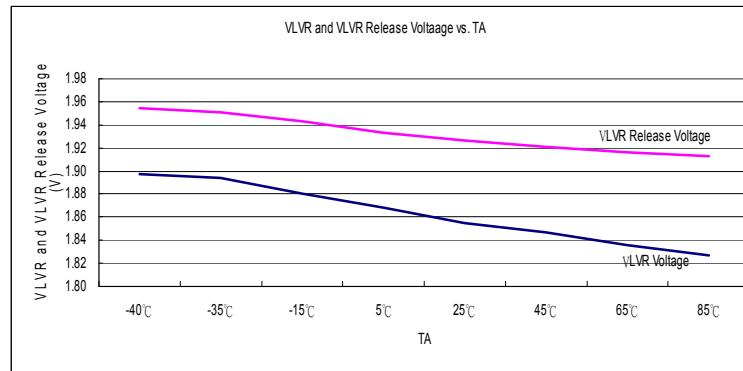


Figure 6.5-3 LVR vs. Temperature

6.6. Power System

$T_A = 25^\circ\text{C}$, $V_{DD} = 3.0\text{V}$, unless otherwise noted

Sym.	Parameter	Test Conditions		Min.	Typ.	Max.	unit
VDDA	VDDA operation current, I_{VDDA}	$I_L = 0\text{mA}$	$VDDAX[1:0]=00b$	22			uA
	Select VDDA output voltage	$I_L = 0.1\text{mA}$, $VDD \geq VDDA + 0.2\text{V}$	$VDDAX[1:0]=00b$	3.3			V
			$VDDAX[1:0]=01b$	2.9			V
			$VDDAX[1:0]=10b$	2.6			V
			$VDDAX[1:0]=11b$	2.4			V
	Dropout voltage	$I_L = 10\text{mA}$	$VDDAX[1:0]=00b$	135			mV
			$VDDAX[1:0]=01b$	150			mV
			$VDDAX[1:0]=10b$	165			mV
			$VDDAX[1:0]=11b$	180			mV
	Temperature drift	$VDDAX[1:0]=11b$	$T_A = -40^\circ\text{C} \sim 85^\circ\text{C}$	50			ppm/°C
	V_{DD} Voltage drift	$I_L = 0.1\text{mA}$	$V_{DD}=2.5\text{V} \sim 3.6\text{V}$	± 0.2			%/V
ACM	ACM operation current, I_{ACM}	$I_L = 0\text{mA}$		20			uA
	Output voltage, V_{ACM}	$ENACM[0]=1$	$I_L = 0\text{uA}$	1.0			V
	Output voltage with Load		$I_L = \pm 200\text{uA}$	0.98	1.02		V_{ACM}
	Temperature drift	$ENACM[0]=1$, $I_L = 10\text{uA}$	$T_A = -40^\circ\text{C} \sim 85^\circ\text{C}$	50			ppm/°C
	VDDA Voltage drift			100			uV/V

VDDA : Adjust Voltage Regulator

ACM : Analog Common Mode Voltage

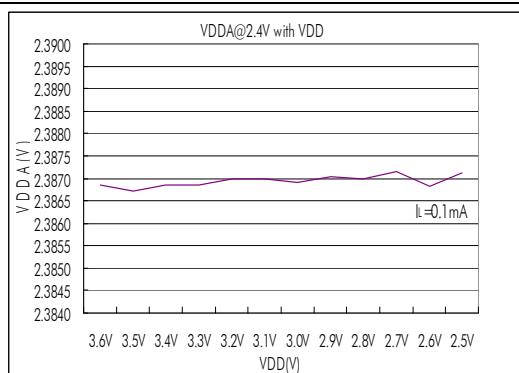


Figure 6.6-1 VDDA $IL=0.1\text{mA}$ vs. VDD

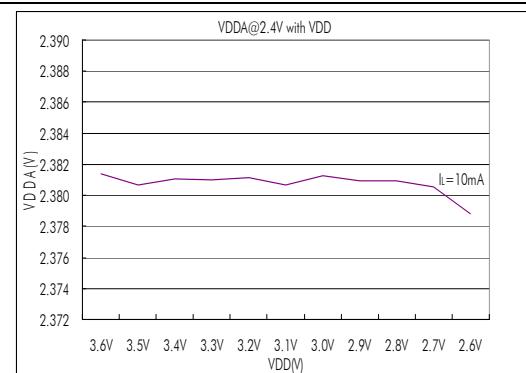


Figure 6.6-2 VDDA $IL=10\text{mA}$ vs. VDD

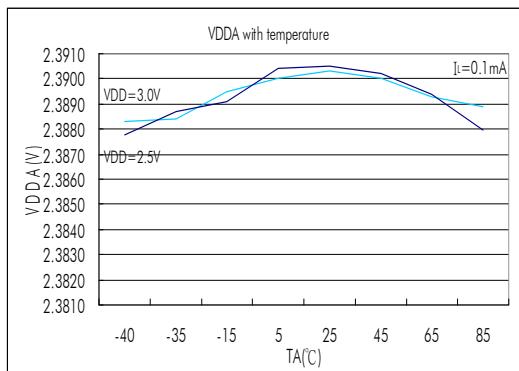


Figure 6.6-3 VDDA IL=0.1mA vs. Temperature

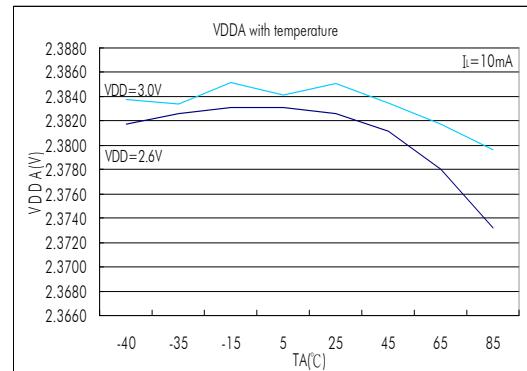


Figure 6.6-4 VDDA IL=10mA vs. Temperature

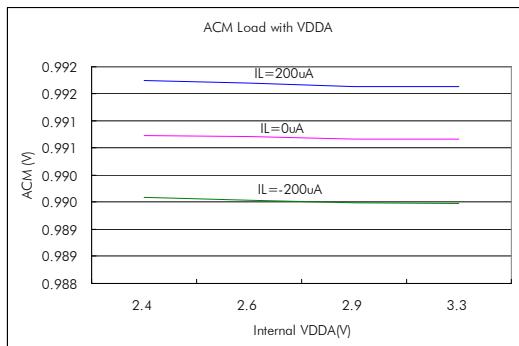


Figure 6.6-5 ACM Load vs. VDDA

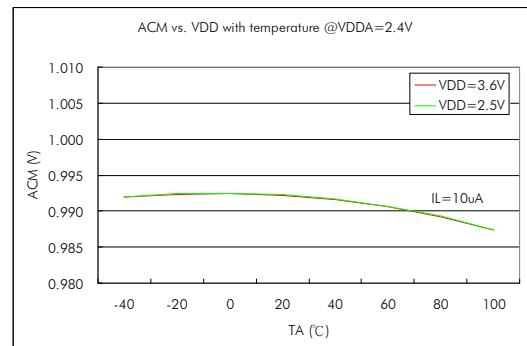


Figure 6.6-6 ACM vs. Temperature

6.7. LCD

$T_A = 25^\circ C, V_{DD} = 3.0V, C_{VLCD} = 4.7\mu F$, unless otherwise noted.

Sym.	Parameter	Test Conditions		Min.	Typ.	Max.	unit
I_{LCD}	Operation supply current without output buffer.(all segment turn on)	LCDPR[0]=1	$V_{DD} = 2.2V$	10			μA
			$V_{DD} = 3.0V$				
VLCD	Supply Voltage at VLCD pin	LCDPR[0]=0		2.2	3.6		V
	Embedded Charge Pump output voltage at VLCD pin	LCDPR[0]=1, $C_{VLCD} = 4.7\mu F$	$V_{DD} = 2.2V, VLCDX[1:0]=11b$	2.295	2.55	2.805	V
			$VLCDX[1:0]=10b$	2.52	2.8	3.08	
			$VLCDX[1:0]=01b$	2.745	3.05	3.355	
			$VLCDX[1:0]=00b$	2.97	3.3	3.63	
Z_{LCD}	Output impedance with LCD buffer	$f_{LCD} = 128Hz, VLCD=3.05V$		10			$k\Omega$

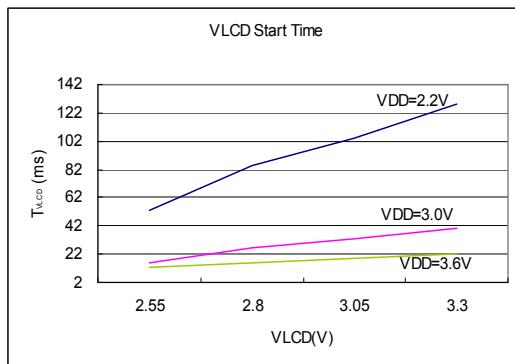


Figure 6.7-1 LCD start time

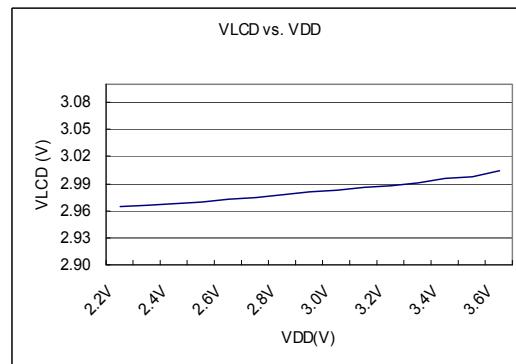


Figure 6.7-2 VLCD vs. VDD

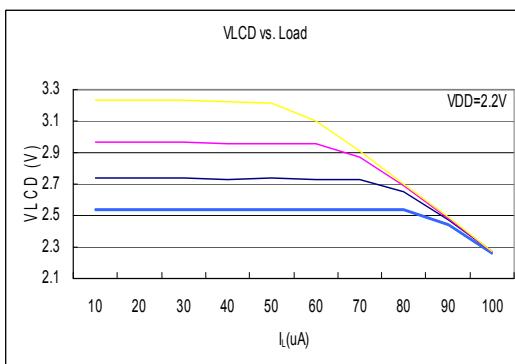


Figure 6.7-3 VLCD vs. I_L @VDD=2.2V

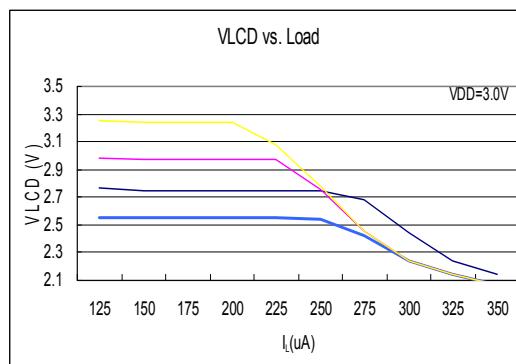


Figure 6.7-4 VLCD vs. I_L @VDD=3.0V

6.8. Low Noise OPAMP

$T_A = 25^\circ\text{C}$, $V_{DD} = 3.0\text{V}$, $VDDA=2.4\text{V}$, unless otherwise noted

Sym.	Parameter	Test Conditions		Min.	Typ.	Max.	unit
V_{LNOP}	Supply voltage at VDDA	ENVDDA[0]=0		2.4	3.6		V
I_{LNOP}	Operation supply current			200			uA
V_{OS-OP}	Input offset voltage without chopper.			OPM[1:0]=1xb	-2	2	mV
	Input offset voltage with chopper			OPM[1:0]=0xb	20		uV
V_{OLR}	Unit gain load regulation	$V_o=1.2\text{V}$, $VDDA=2.4\text{V}$	OPM[1:0]=00b	$T_A=-40^\circ\text{C} \sim 85^\circ\text{C}$	0.1		$\text{uV}/^\circ\text{C}$
			OPM[1:0]=10		2		
$CMVR$	Common-mode voltage input range			OPM[1:0]=xxb	0.1	$VDDA-1.1$	V
$CMRR$	Common-mode rejection ratio			OPM[1:0]=xxb	90		dB

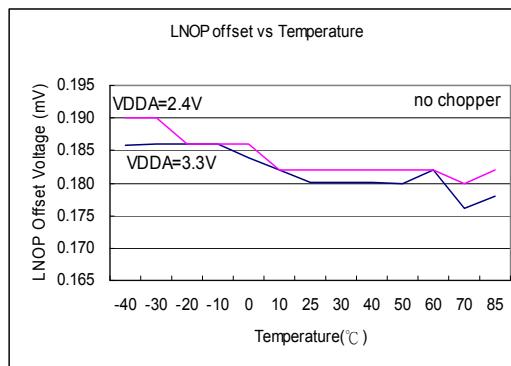


Figure 6.8-1 LNOP Offset Temperature

6.9. SD18, Power Supply and Recommended Operating Conditions

T_A = 25°C, V_{DD} = 3.0V, VDDA=2.4V, unless otherwise noted

Sym.	Parameter	Test Conditions		Min.	Typ.	Max.	unit		
V _{SD18}	Supply Voltage at VDDA	ENVDDA[0]=0		2.4	3.6		V		
f _{SD18}	Modulator sample frequency, ADC_CK			25	250	300	KHz		
	Over Sample Ratio, OSR			256	32768				
I _{SD18}	Operation supply current without PGA	ENADC[0]=1 INBUF[0]=1,VRBUF[0]=0		GAIN =4, ADC_CK=250KHz	168		uA		
		ENADC[0]=1 INBUF[0]=0,VRBUF[0]=1			150				
		ENADC[0]=1 INBUF[0]=0,VRBUF[0]=0			120				

6.9.1 PGA, Power Supply and Recommended Operating Conditions

T_A = 25°C, V_{DD} = 3.0V, VDDA=2.4V, unless otherwise noted

Sym.	Parameter	Test Conditions		Min.	Typ.	Max.	unit
V _{PGA}	Supply Voltage at VDDA	ENVDDA[0]=0		2.4	3.6		V
I _{PGA}	Operation supply current	PGAGN[1:0]=<01>or<1x>			320		uA
G _{PGA}	Gain temperature drift	T _A = -40°C ~ 85°C	GAIN=128		5		ppm/°C

6.9.2 SD18, Performance II (fSD18=250KHz)

T_A = 25°C, V_{DD} = 3.0V, VDDA=2.9V,V_{VR}=1.0V,GAIN=1 without PGA, unless otherwise noted

Sym.	Parameter	Test Conditions		Min.	Typ.	Max.	unit				
INL	Integral Nonlinearity(INL)	VDDA=2.4V,V _{VR} =1.0V, ΔSI=±200mV		±0.003	±0.01	%FSR					
		VDDA=2.4V,V _{VR} =1.0V, ΔSI=±450mV									
	No Missing Codes ³	ADC_CK=250KHz,OSR[2:0]=010b		23			Bits				
G _{SD18}	Temperature drift Gain 1~x16 (INBUF[0]=0b.) Gain 1~x4 (INBUF[0]=1b.)	INBUF[0]=0b,VRBUF[0]=0b		T _A = -40°C ~ 85°C	2	ppm/°C					
		INBUF[0]=1b,VRBUF[0]=0b									
		INBUF[0]=0b,VRBUF[0]=1b									
		INBUF[0]=1b,VRBUF[0]=1b									
E _{OS}	Offset error of Full Scale Rang input voltage range with Chopper and Buffer(INBUF,VRBUF) without PGA		△ AI=0V △ VR=0.9V DCSET[2:0]=<000>	Gain=2	1		%FSR				
	Offset error of Full Scale Rang input voltage range with Chopper without PGA and Buffer(INBUF,VRBUF)				1						
	Offset temperature drift with chopper without PGA and Buffer (INBUF,VRBUF).				2						
			* △ AI is external short	Gain=2	1						
					GAIN=1						
					0.5						

HY11P13

Embedded 18-Bit $\Sigma\Delta$ ADC

8-Bit RISC-like Mixed Signal Microcontroller

		GAIN=16	0.15	
	Offset temperature drift with chopper and Buffer (INBUF,VRBUF) without PGA.	GAIN=1	2	
		GAIN=2	1	
		GAIN=4	0.5	
	Offset temperature drift with chopper without Buffer (INBUF,VRBUF).	GAIN=128	0.02	
CM _{SD18}	Common-mode rejection	V _{CM} =0.7V to 1.7V, V _{VR} =1.0V,without PGA	V _{SI} =0V, GAIN=1	90
		V _{CM} =0.7V to 1.7V, V _{VR} =1.0V, without PGA	V _{SI} =0V, GAIN=16	75
PSRR	DC power supply rejection	VDDA=3.0V, Δ VDDA=± 100mV,V _{VR} =1.0V, V _{SI} =1.2V,V _{SL} =1.2V,	GAIN=1 PGA=off	75
			GAIN=16 PGA=8	

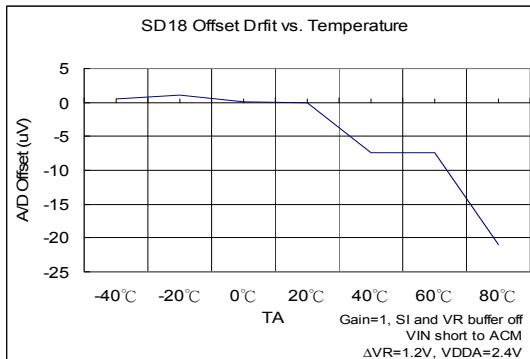


Figure 6.9-1(a) SD18 Offset Temperature Drift

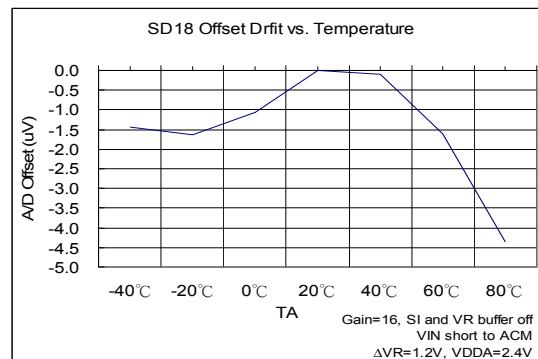


Figure 6.9-1(b) SD18 Offset Temperature Drift

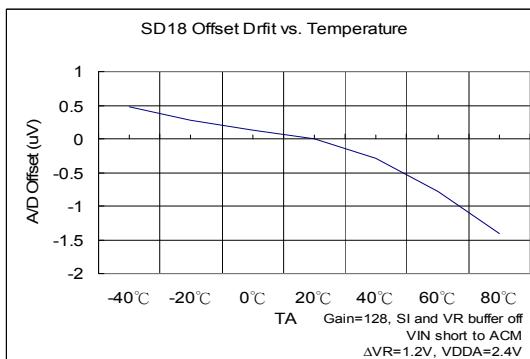


Figure 6.9-1(c) SD18 Offset Temperature Drift

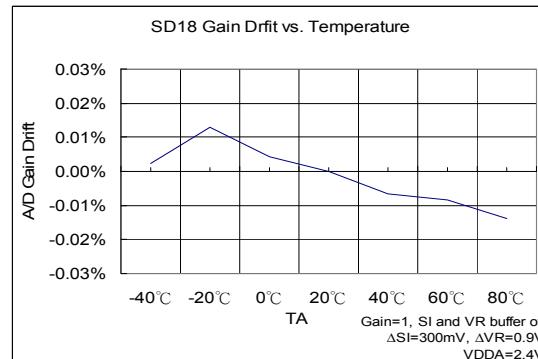


Figure 6.9-2(a) SD18 Gain Drift with Temperature

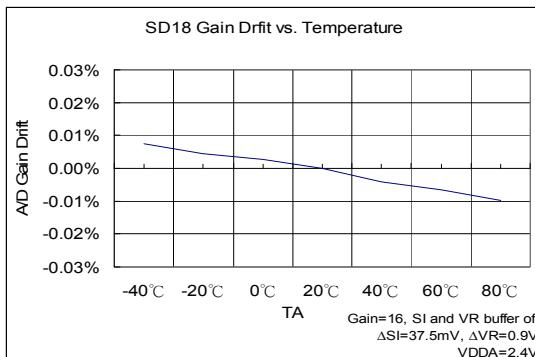


Figure 6.9-2(b) SD18 Gain Drift with Temperature

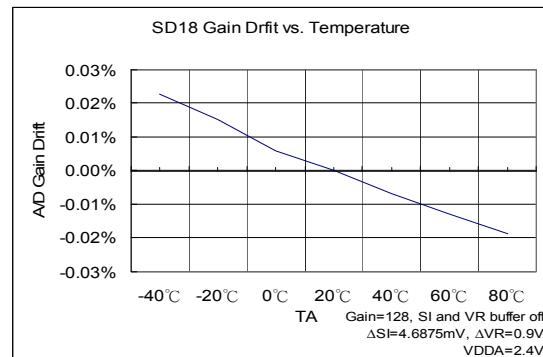


Figure 6.9-2(c) SD18 Gain Drift with Temperature

6.9.3 SD18, Temperature Sensor

$T_A = 25^\circ\text{C}$, $V_{DD} = 3.0\text{V}$, $VDDA=3.3\text{V}$, unless otherwise noted

Sym.	Parameter	Test Conditions	Min.	Typ.	Max.	unit
TC_S	Sensor temperature drift	$\Delta VR=2.4\text{V}, VRGN[0]=1,$ $INBUF[0]=1$	178		$\mu\text{V}/^\circ\text{C}$	
KT	Absolute Temperature Scale 0°K		-289		$^\circ\text{C}$	
TC_{ERR}	One point calibrate error temperature		Calibration at 25°C of $-40^\circ\text{C}\sim85^\circ\text{C}$		± 2	

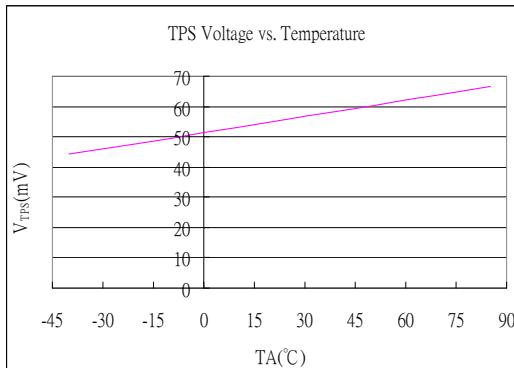


Figure 6.9-3 TPS Output Voltage vs. Temperature Drift

6.9.4 SD18 Noise Performance

$T_A = 25^\circ\text{C}$, $V_{DD} = 3.0\text{V}$, $VDDA=2.4\text{V}$, unless otherwise noted

HY11P13 provides important input noise specification that aims at SD18. Table 6.9-4(a) and Table 6.9-4(b) lists out the relations of typical noise specification, gain, output rate and maximum input voltage of single end. Test conditions are external input signal short, voltage reference: 1.2V and 1024 records were sampled.

ENOB(RMS) with OSR/GAIN at A/D Clock=250Khz, VDDA=2.4V, VREF=1.2V													
Max. Vin(mV) =0.9*VREF ⁽¹⁾	OSR			256	512	1024	2048	4096	8192	16384	32768		
	Output rate(HZ)			977	488	244	122	61	31	15	8		
	Gain	=	PGA	×	ADGN								
±2400	0.25	=	1	×	0.25	16.3	17.4	17.9	18.5	19.0	19.5	20.0	20.4
±2160	0.5	=	1	×	0.5	16.3	17.3	17.9	18.4	18.9	19.4	19.8	20.2
±1080	1	=	1	×	1	16.2	17.2	17.8	18.3	18.8	19.3	19.7	20.1
±540	2	=	1	×	2	16.1	17.1	17.6	18.2	18.7	19.2	19.6	20.0
±270	4	=	1	×	4	16.0	16.9	17.5	18.0	18.5	18.9	19.4	19.8
±135	8	=	1	×	8	15.9	16.6	17.2	17.7	18.2	18.7	19.2	19.6
±68	16	=	1	×	16	15.6	16.3	16.8	17.3	17.7	18.3	18.8	19.3
±34	32	=	2	×	16	14.8	15.3	15.9	16.4	16.9	17.4	17.8	18.3
±17	64	=	4	×	16	14.5	15.0	15.5	16.0	16.5	17.0	17.5	18.0
±8	128	=	8	×	16	14.0	14.6	15.1	15.6	16.0	16.6	17.0	17.5

(1) Max.Vin (mV) is the max. input voltage of single end to ground (VSS).

Table 6.9-4(a) SD18 ENOB Table

RMS Noise(uV) with OSR/GAIN at A/D Clock=250Khz, VDDA=2.4V, VREF=1.2V													
Max. Vin(mV) =0.9*VREF	OSR			256	512	1024	2048	4096	8192	16384	32768		
	Output rate(HZ)			977	488	244	122	61	31	15	8		
	Gain	=	PGA	×	ADGN								
±2400	0.25	=	1	×	0.25	121.08	57.40	38.74	26.66	18.39	13.21	9.49	6.98
±2160	0.5	=	1	×	0.5	61.63	29.23	19.21	13.51	9.78	7.02	5.12	3.91
±1080	1	=	1	×	1	32.21	15.70	10.25	7.31	5.19	3.77	2.80	2.13
±540	2	=	1	×	2	16.59	8.54	5.91	4.06	2.86	2.06	1.48	1.12
±270	4	=	1	×	4	9.00	4.84	3.33	2.37	1.67	1.19	0.87	0.65
±135	8	=	1	×	8	5.04	2.97	2.02	1.44	1.01	0.73	0.51	0.39
±68	16	=	1	×	16	3.03	1.84	1.29	0.92	0.70	0.46	0.33	0.24
±34	32	=	2	×	16	2.61	1.81	1.27	0.89	0.62	0.45	0.32	0.23
±17	64	=	4	×	16	1.66	1.13	0.80	0.56	0.41	0.29	0.20	0.14
±8	128	=	8	×	16	1.13	0.77	0.55	0.38	0.28	0.19	0.14	0.10

Table 6.9-4(b) SD18 RMS Noise Table

The RMS noise are referred to the input. The Effective Number of Bits (ENOB(RMS Bit)) is defined as:

$$\text{ENOB(RMS)} = \frac{\ln\left(\frac{\text{FSR}}{\text{RMS Noise}}\right)}{\ln(2)}$$

$$\text{RMS Noise} = \frac{\left(2 \times \text{VREF} \times \sqrt{\sum_{k=1}^{1024} (\text{ADO}[k] - \text{Average})^2}\right)}{2^{23}}$$

Where FSR (Full-Scale Range) = $2 \times \text{VREF}/\text{Gain}$.

$$\text{Average} = \frac{\sum_{k=1}^{1024} (\text{ADO}[k])}{1024}$$

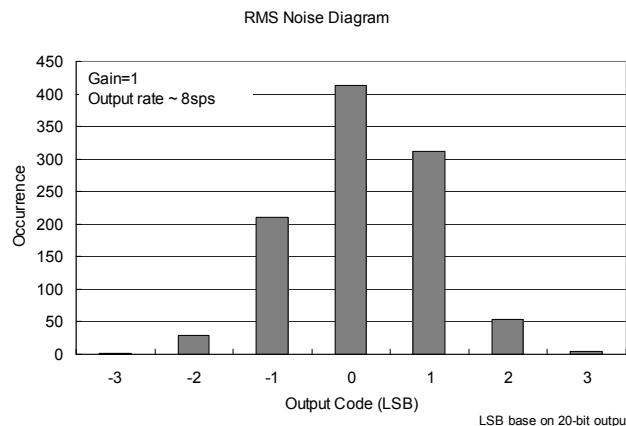


Figure 6.9-4(a) RMS Noise Diagram

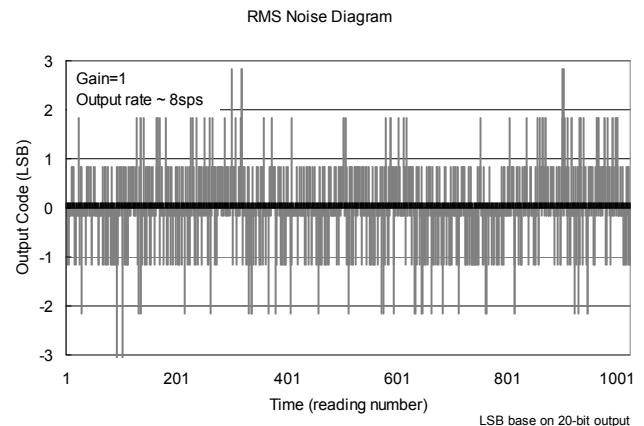


Figure 6.9-4(b) Output Code Diagram

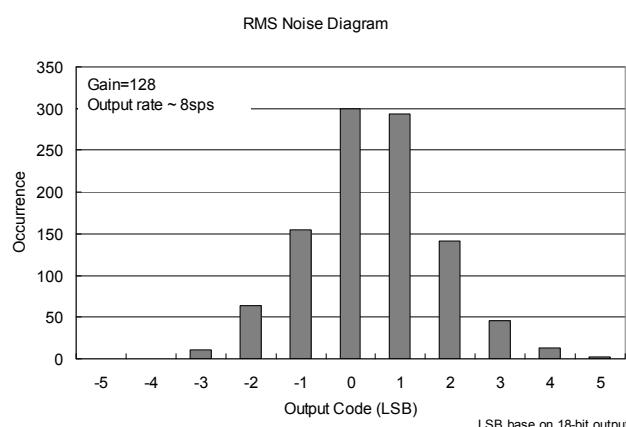


Figure 6.9-4(c) RMS Noise Diagram

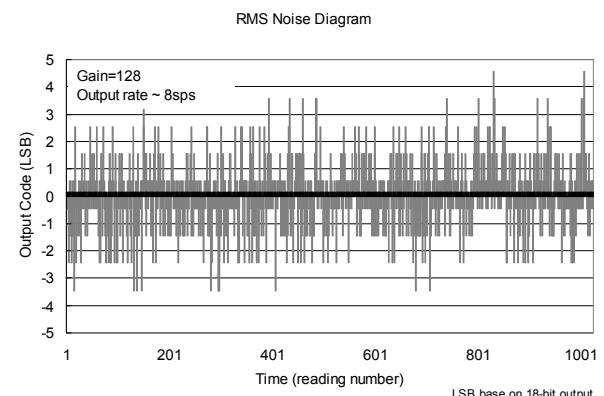


Figure 6.9-4(d) Output Code Diagram

7. Ordering Information

Device No.¹	Package Type	Pins	Package Drawing		Code²	Shipment Packing Type	Unit Q'ty	Material Composition	MSL³
HY11P13-D000	Die	-	D	000	000	-	100	Green ⁴	-
HY11P13-L064	LQFP	64	L	064	000	Tray	160	Green ⁴	MSL-3
HY11P13-LS64	LQFP	64	L	S64	000	Tray	250	Green ⁴	MSL-3

¹ Device No.: Model No. – Package Type Description – Code (Blank Code/ Standard/ Customized Programming Code)

Ex: Your customized programming code is 008 and you require die shipment.

The device No. will be HY11P13-D000-008.

Ex: You request blank code in die package.

The device No. will be HY11P13-D000.

Ex: You request blank code in LQFP 64 package.

The device No. will be HY11P13-L064.

And please clearly indicate the shipment packing type when placing orders.

Ex: Your customized programming code is 009 and you require products in LQFP 64 package.

The device No. will be HY11P13-LS64-009.

And please clearly indicate the shipment packing type when placing orders.

² Code:

“001”~ “999” is standard or customized programming code. Blank code does not have these numbers.

³ MSL:

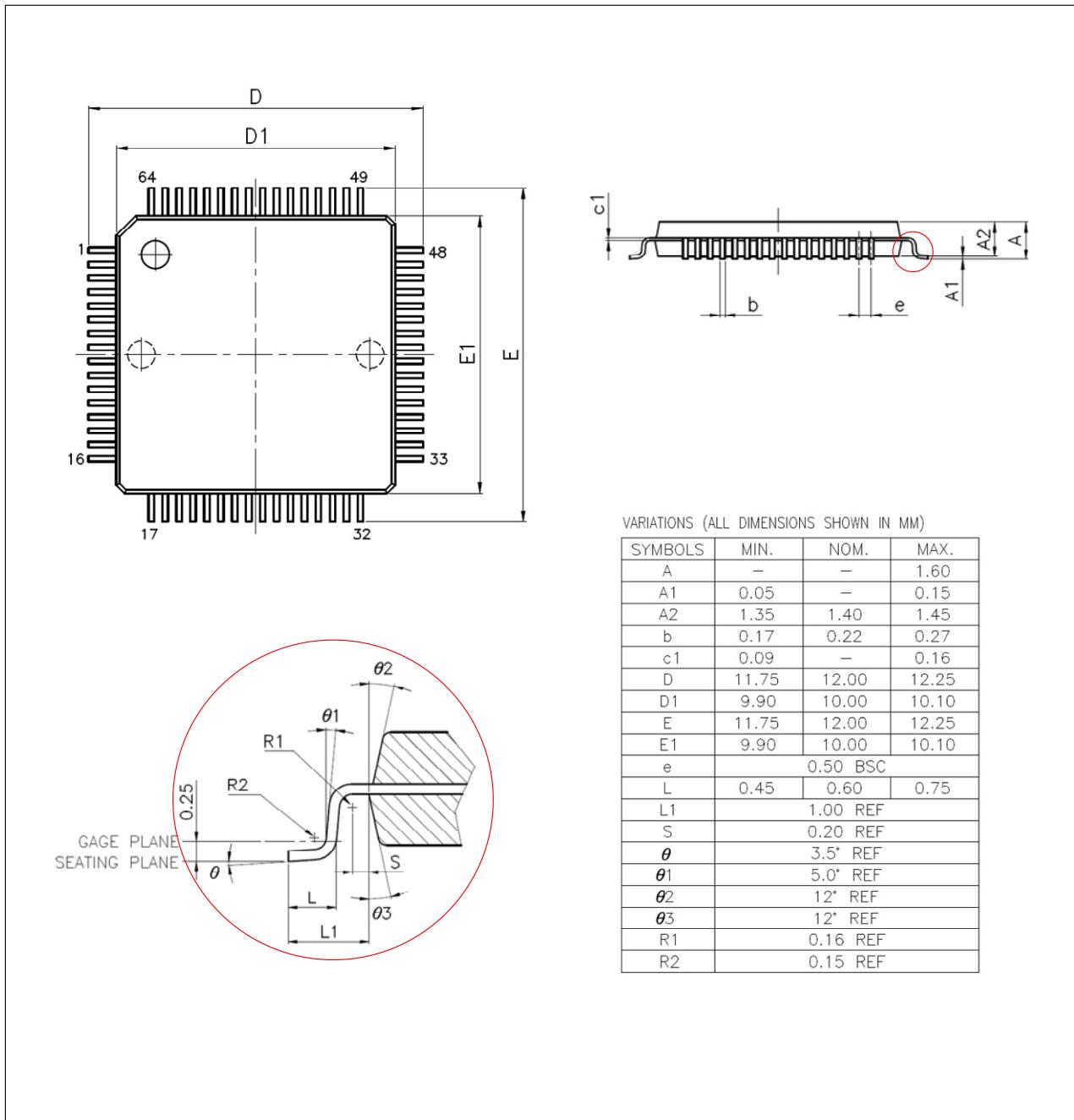
The Moisture Sensitivity Level ranking conforms to IPC/JEDEC J-STD-020 industry standard categorization. The products are processed, packed, transported and used with reference to IPC/JEDEC J-STD-033.

⁴ Green (RoHS & no Cl/Br):

HYCON products are Green products that compliant with RoHS directive and are Halogen free (Br/Cl<0.1%).

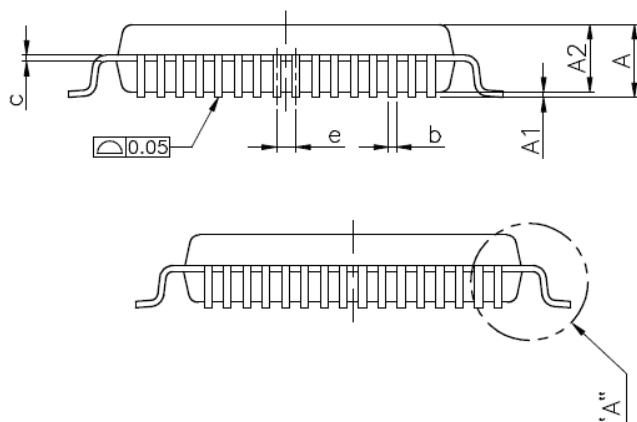
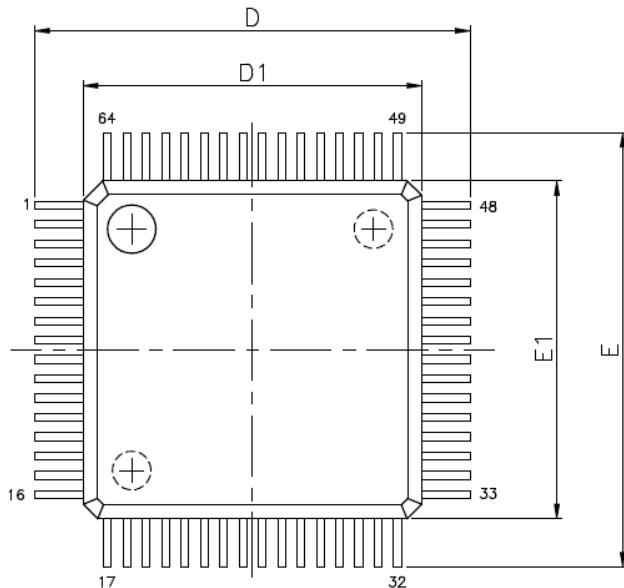
8. Package Information

8.1. LQFP64 (L064)



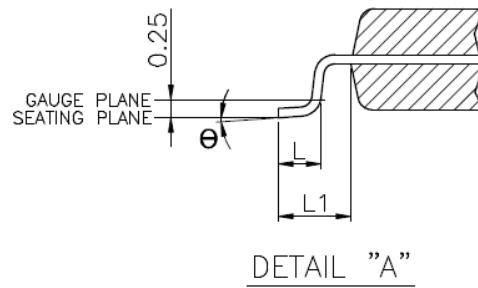
JEDEC MS-026 compliant

8.2. LQFP64(LS64)



VARIATIONS (ALL DIMENSIONS SHOWN IN MM)

SYMBOLS	MIN.	NOM.	MAX.
A	—	—	1.60
A1	0.05	—	0.15
A2	1.35	1.40	1.45
b	0.13	0.18	0.23
c	0.09	—	0.20
D	9.00	BSC	
D1	7.00	BSC	
e	0.40	BSC	
E	9.00	BSC	
E1	7.00	BSC	
L	0.45	0.60	0.75
L1	1.00	REF	
Θ	0°	3.5°	7°



JEDEC MS-026 compliant

9. Revision Record

Major differences are stated thereafter:

Version	Page	Revision Summary
V04	ALL	First edition
V06		With reference to documentation: DS-HY11P13-V06_TC
	4	Features revision
	6~8	Table 2-1 Pin Definition and Function Description revision
	8~13	Chapter 3 Application Circuit revision
	24~25	Chapter 6.6 Power System revision
	26	Chapter 6.8 Low Noise OPAMP revision
	28~30	Chapter 6.9.2 SD18, Performance II revision
V07	15~16	Chapter 5 Register List revision
V08	4	Features revision
	9~10	Chapter 3.1 & 3.2 content revision
	24~25	Chapter 6.6 Power System revision
V09	1	Cover Revised
	5	Feature revised, delete 1/2bias description
	6	Add in Note 3 description
	10~14	Revised application circuit, added in RC circuit of RST
	15	Revised Internal Block Diagram
V13	4	Revise Chapter 1 content
	10	Revise Figure 3-2
	11	Revise Figure 3-3
	15	Revise Development Tool Related Operating Instruction serial numbers
	16	Add in SD18 Network chapter
	19	Revise Chapter 6
	26	Revise temp. drift spec of power system
	28	Reduce LCD current spec.
	34~35	Add in the chapter of SD18 Noise Performance
	36	Chapter 7 Ordering information revision
	38	Add in package information – 8.2 LQFP64(LS64)
V14	17	Added in 4.4 Low Noise OPAMP Network